

EE 435

Lecture 39

References and Bias Generators

Final Exam:

Scheduled on Final Exam Schedule:

Wednesday May 5 9:45 a.m.

Revised Final Exam:

- Take-home format – open book and open notes
- Will be posted on course WEB site by late Friday April 30
- Due at 5:00 p.m. on Wednesday May 5 : Upload as pdf file into Canvas

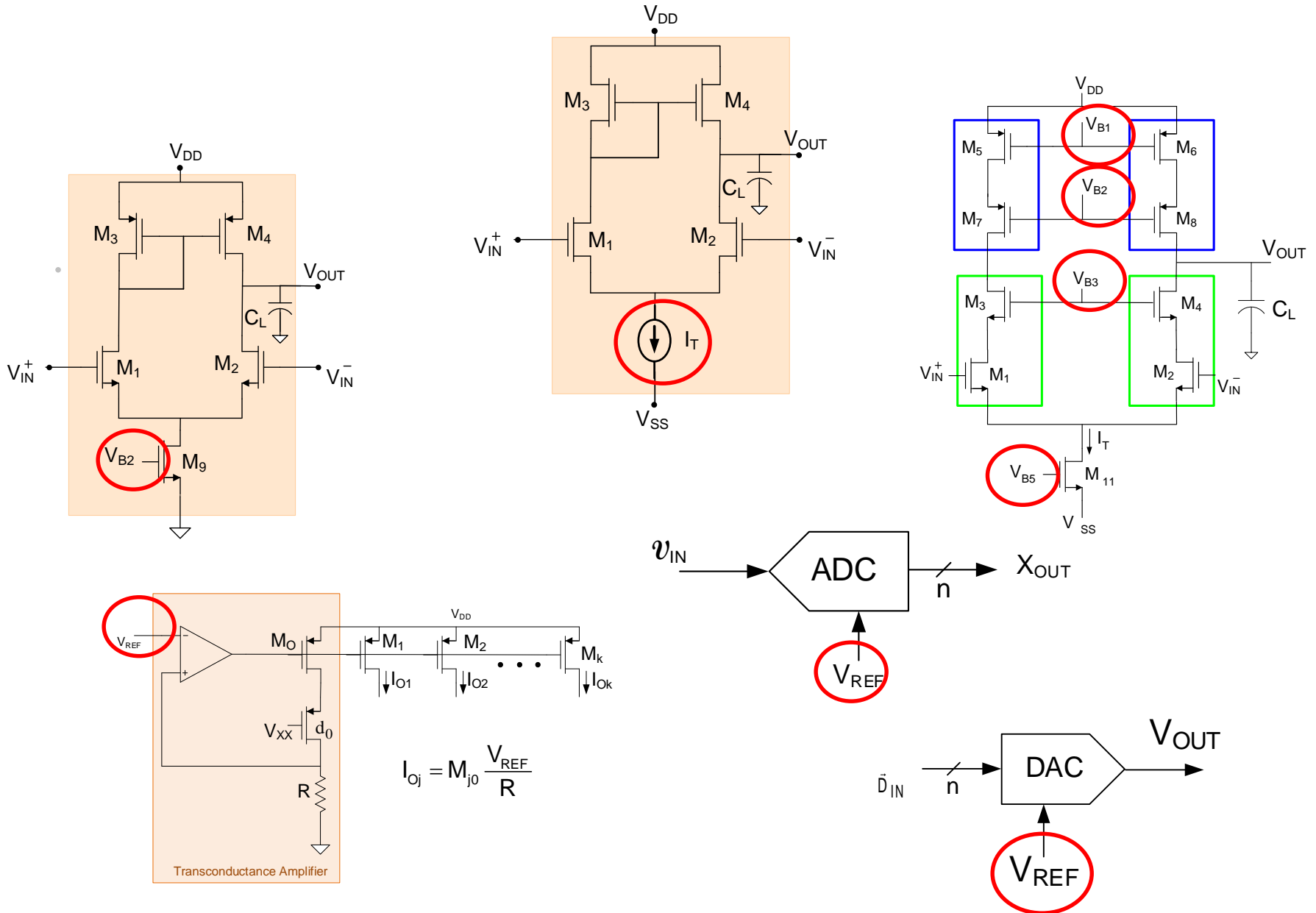
If anyone has any constraints of any form such as internet access or other factors that makes it difficult to work with this revised format, please contact Professor Geiger by 5:00 p.m. on Wednesday April 28

Bias Voltages/Currents and References

How do we get quantities such as voltage, current, resistance, temperature, ?.... in an electronic circuit

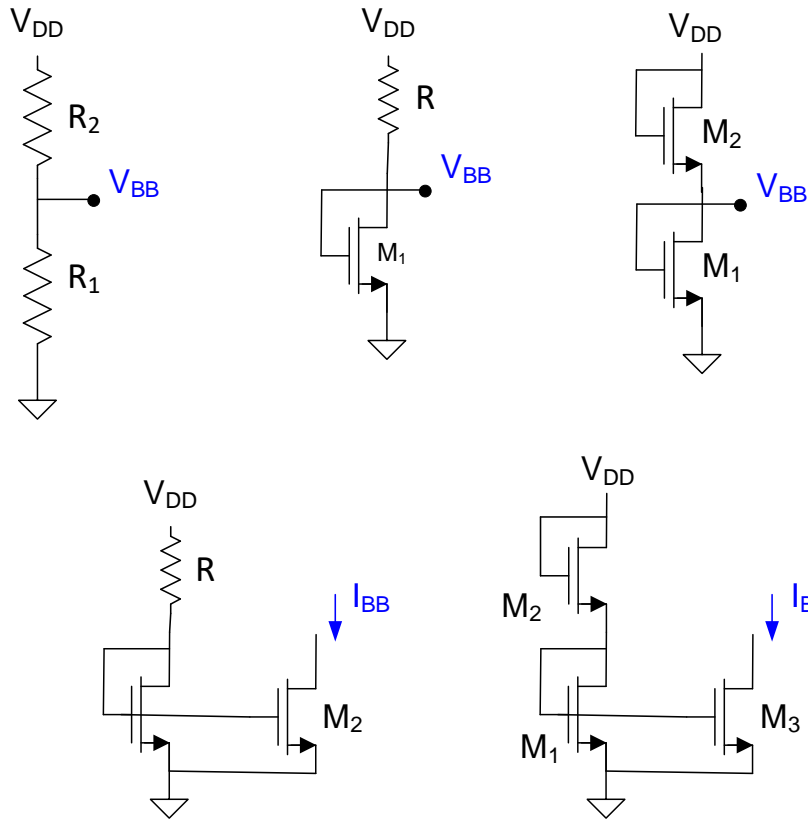
Bias Voltages/Currents and References

How are these voltages and currents generated?



Bias Voltages/Currents and References

How are these voltages and currents generated?



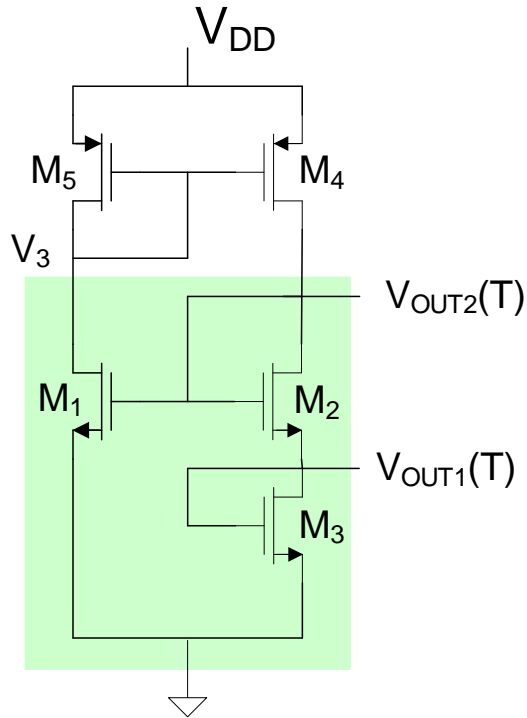
All will work !

Termed Supply-Referenced Sources

But supply sensitivity (supplies usually poorly controlled and noisy) process dependence, and temperature dependence unacceptable in many applications

Bias Voltages/Currents Generators

How are these voltages and currents generated?



Inverse-Widlar

$$V_{O1} = V_{Tn} \left(\frac{1 - \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}}{1 + \sqrt{\frac{W_2 L_3}{W_3 L_2}} - \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}} \right)$$

$$V_{O2} = V_{Tn} \left(\frac{1 + \sqrt{\frac{W_2 L_3}{W_3 L_2}} - 2 \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}}{1 + \sqrt{\frac{W_2 L_3}{W_3 L_2}} - \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}} \right)$$

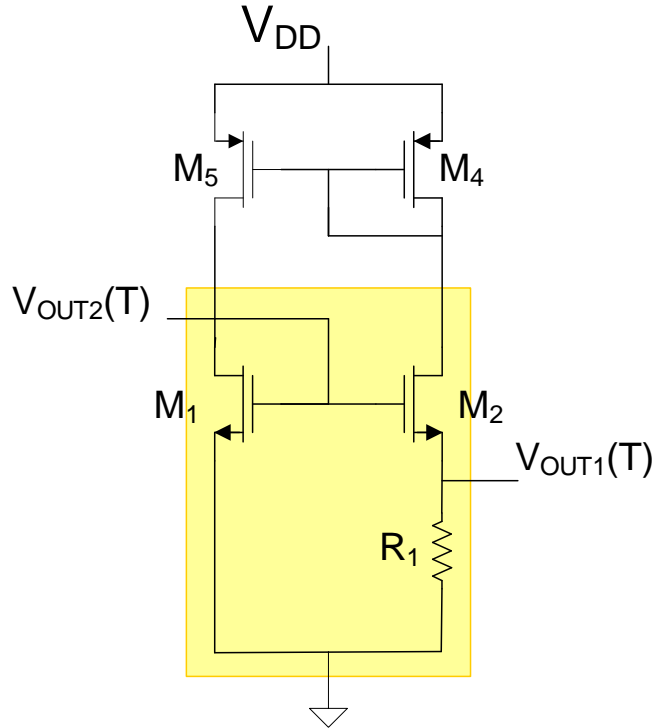
M_{54} is the $M_5:M_4$ Current Mirror Gain

Supply-independent Bias Generator!

Start-up circuit needed (notice positive feedback loop)

Supply-independent Bias Generators Widely Used

Bias Voltages/Currents Generators



Widlar Generator !

$$V_{O1} = \left(\frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left(\frac{\theta_1}{2} \right)^2} \right) \left(1 - \sqrt{\frac{W_1 L_2}{M_{45} W_2 L_1}} \right)$$

$$V_{O2} = V_{Tn} + \frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left(\frac{\theta_1}{2} \right)^2}$$

where

$$\theta_1 = \frac{M_{45} 2L_1}{R \mu_n C_{OX} W_1}$$

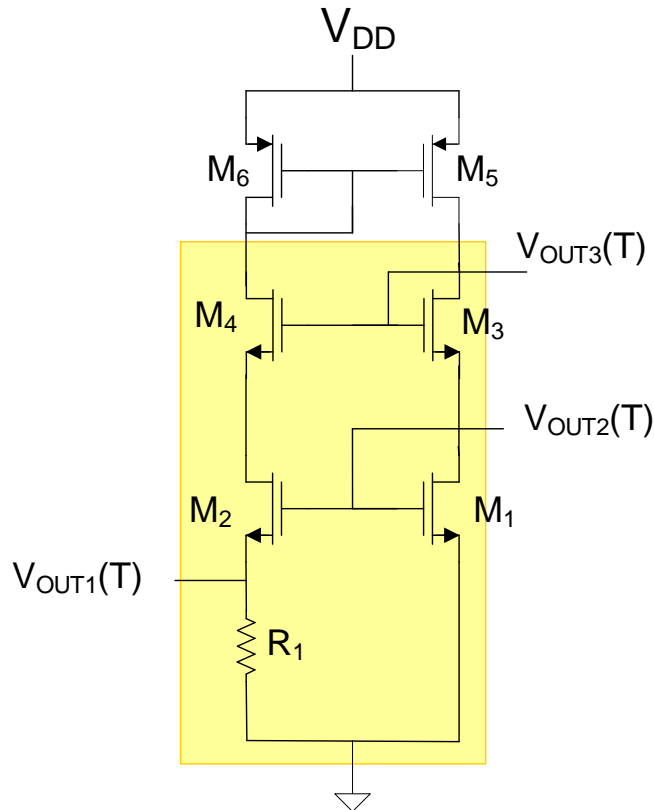
M_{45} is the $M_4:M_5$ Current Mirror Gain

Supply-independent Bias Generator!

Start-up circuit needed (notice positive feedback loop)

Supply-independent Bias Generators Widely Used

Bias Voltages/Currents Generators



Martin Johns Page 307

$$V_{O1} = \left(\frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left(\frac{\theta_1}{2} \right)^2} \right) \left(1 - \sqrt{\frac{W_1 L_2}{M_{65} W_2 L_1}} \right)$$

$$V_{O2} = V_{Tn} + \frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left(\frac{\theta_1}{2} \right)^2}$$

where

$$\theta_1 = \frac{M_{65} 2L_1}{R \mu_n C_{OX} W_1}$$

M_{65} is the $M_6:M_5$ Current Mirror Gain

Widlar Generator !

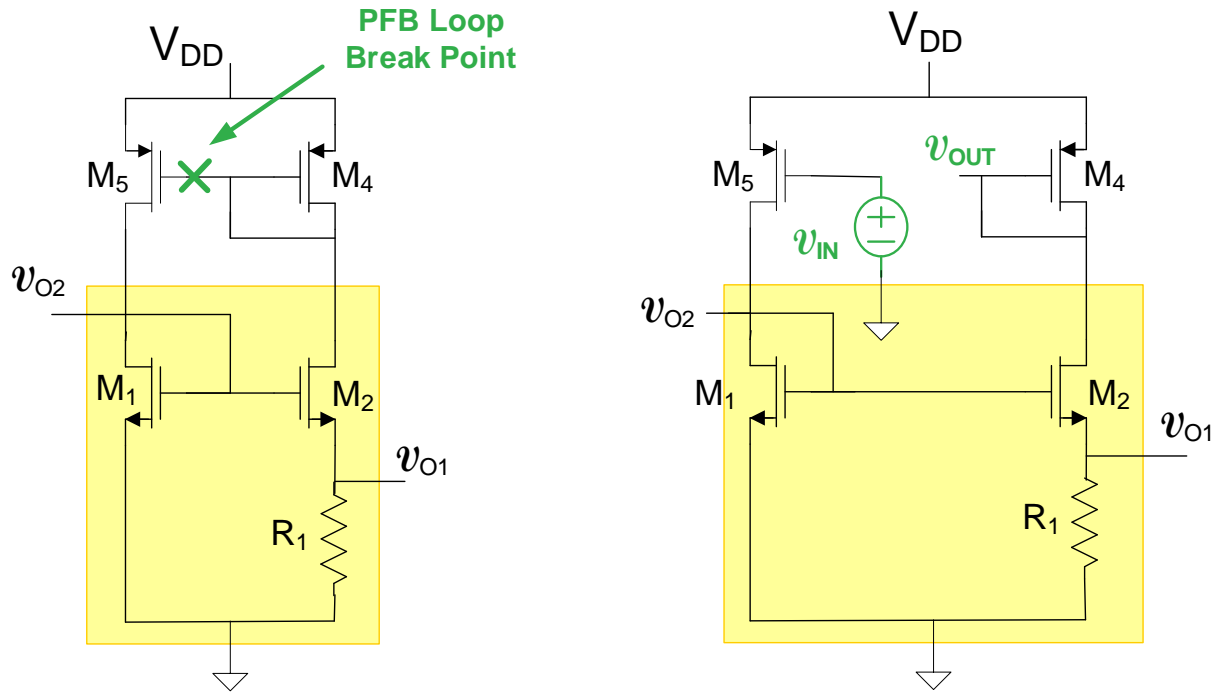
Supply-independent Bias Generator!

Start-up circuit needed (notice positive feedback loop)

Supply-independent Bias Generators Widely Used

Bias Voltages/Currents Generators

Need for Start-up Circuit



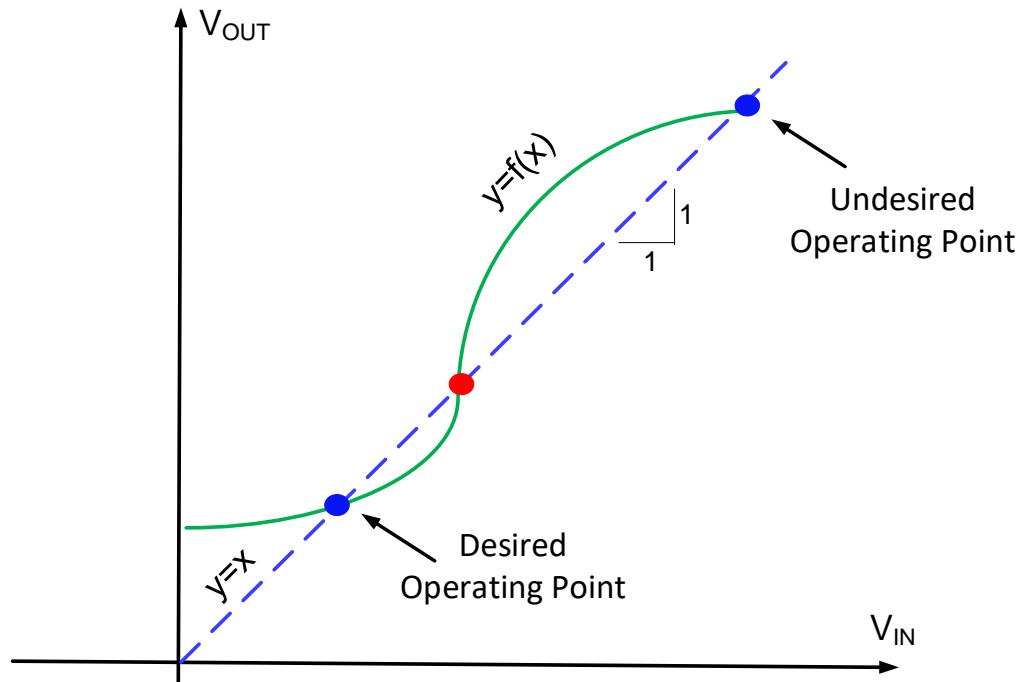
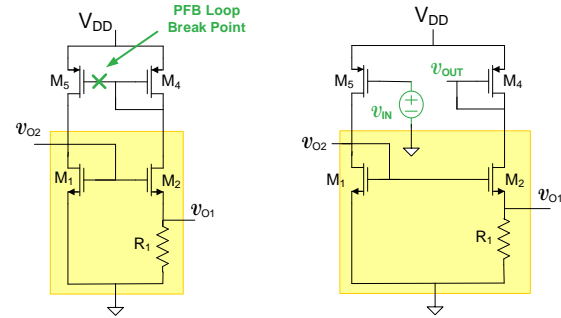
$V_{OUT}=f(V_{IN})$ termed the return map

Termed Homotopy Analysis

Must not perturb operating point when breaking loop !

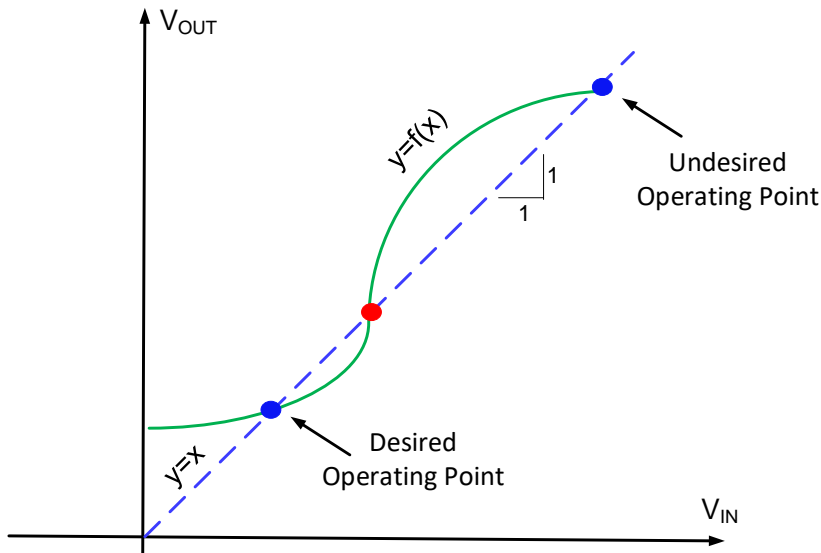
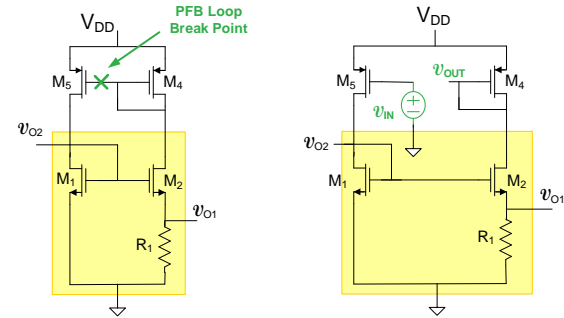
Bias Voltages/Currents Generators

Need for Start-up Circuit

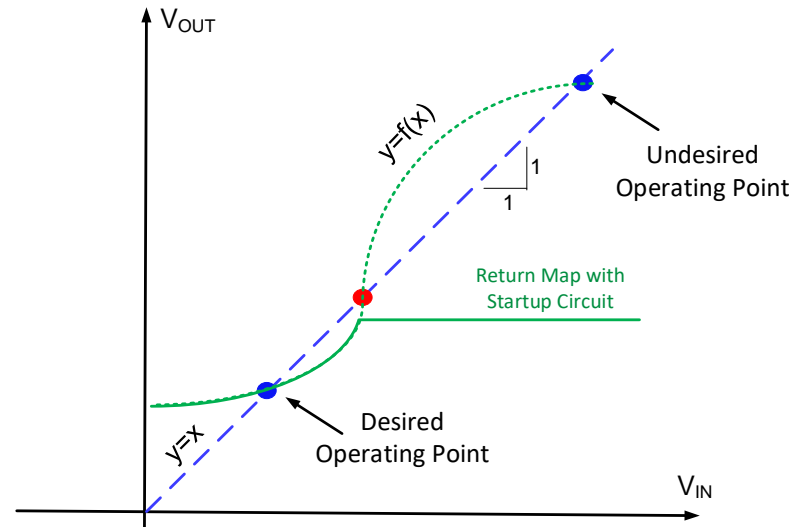


Bias Voltages/Currents Generators

Need for Start-up Circuit



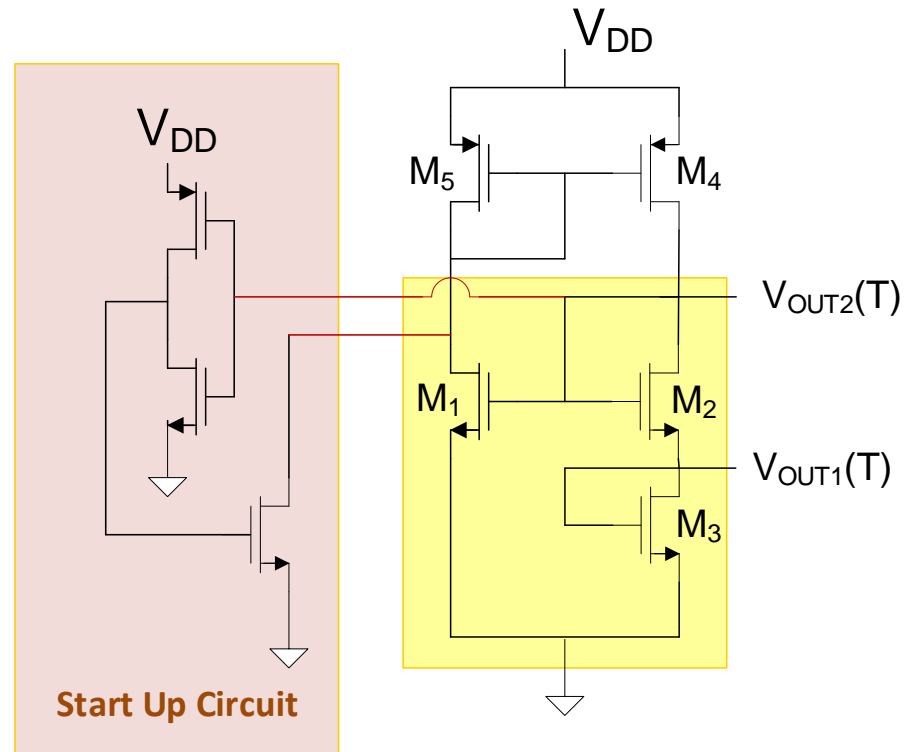
Without start-up circuit



With start-up circuit

Must verify start-up is effective over PVT variations

Bias Voltages/Currents Generators



Several different start-up circuits have been used

This start-up circuit shuts off during normal operation !

Bias Voltages/Currents Generators

Often prefer bias generators whose output changes with process parameters

Better biases many linear circuits (e.g. op amps)

But these bias generators, though simple, are process and temperature dependent

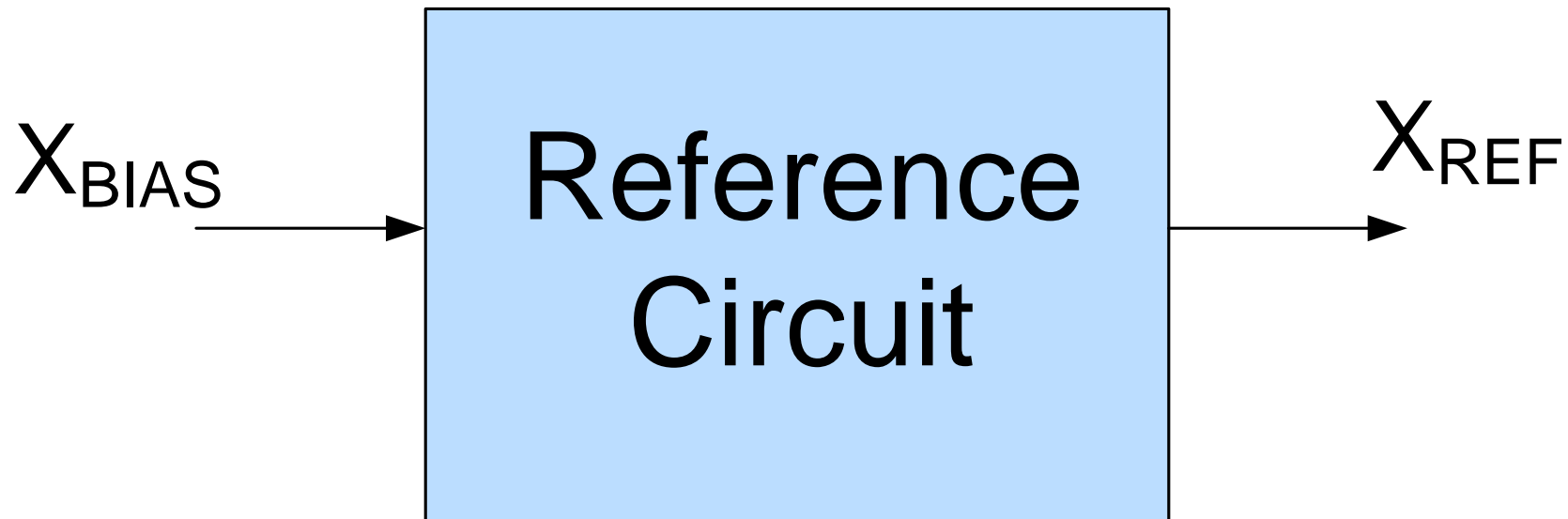
The term “References” usually refers to generators that are ideally independent of supply, process, and temperature

Types of References

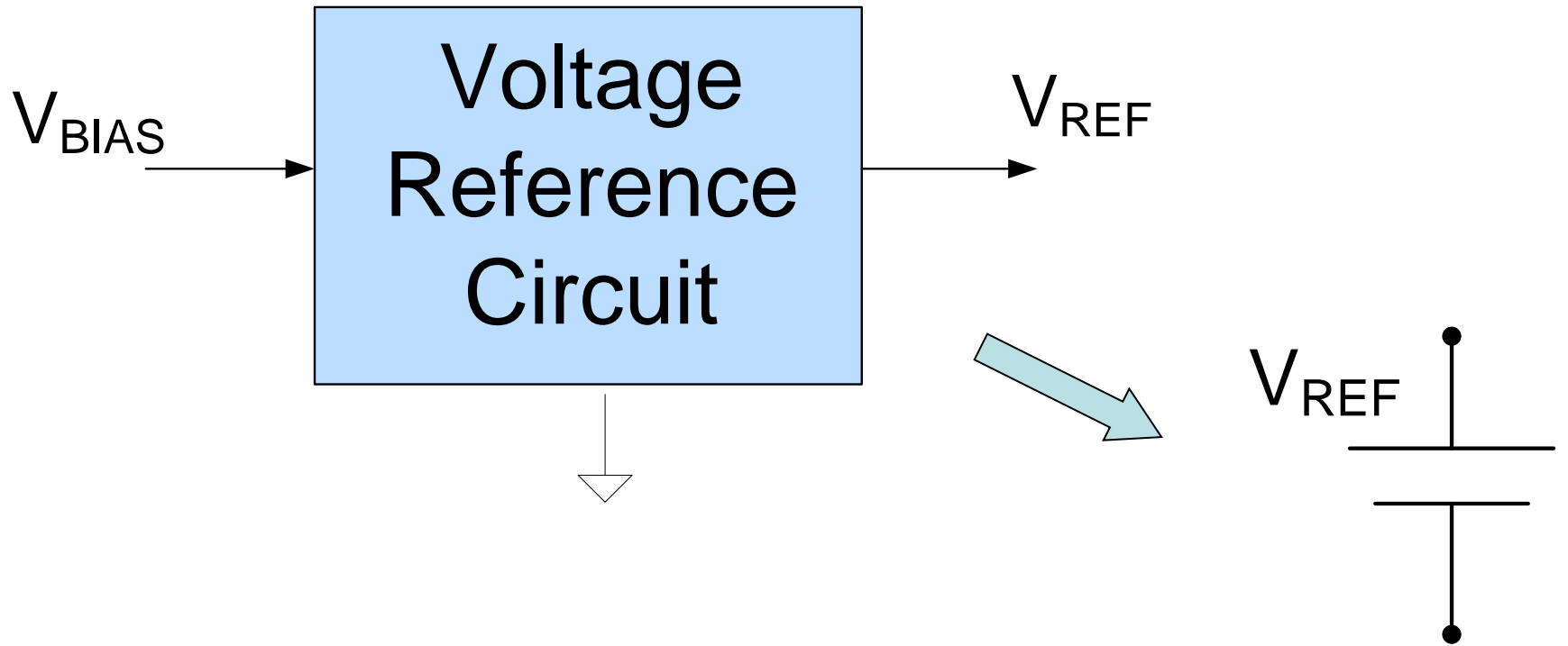
- Voltage References
- Current References
- Time References
-

Sensors Closely Related

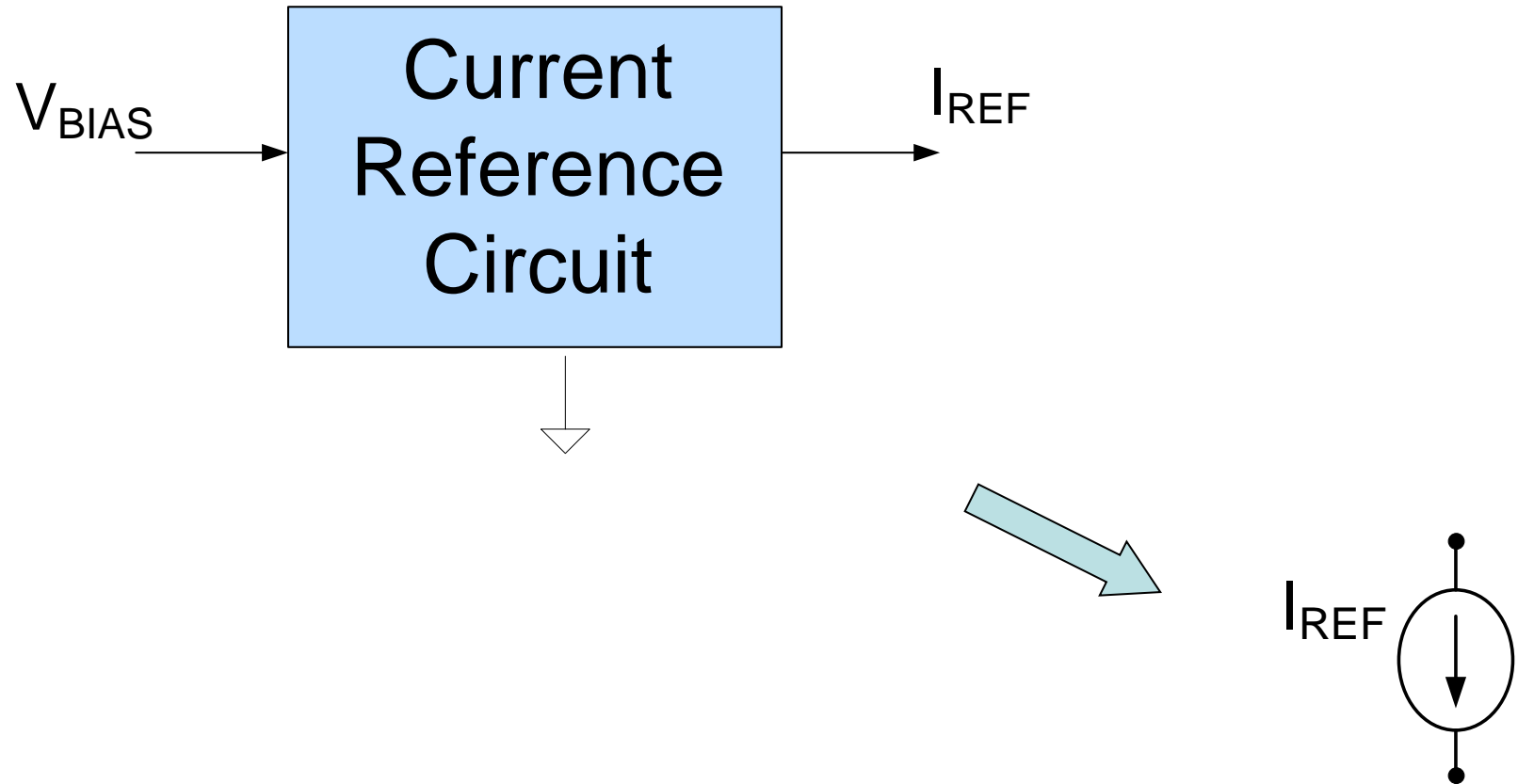
- Temperature
- Period
- Resistance
- Capacitance
-



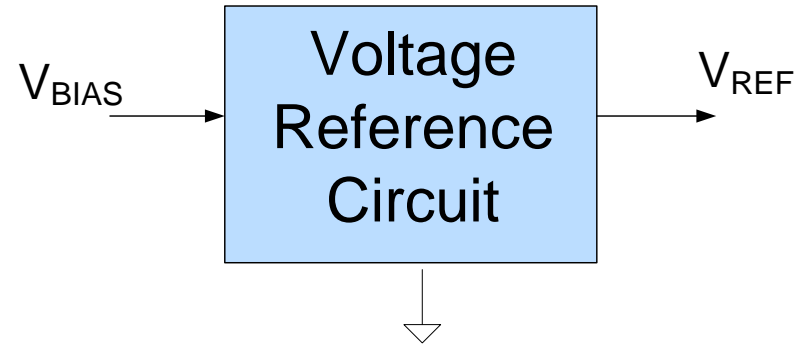
Voltage Reference



Current Reference

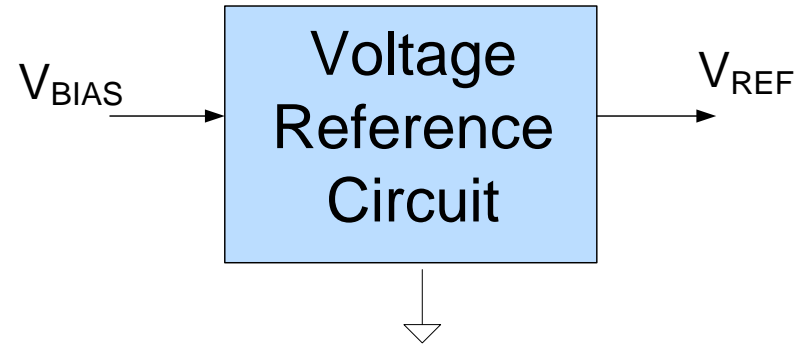


Desired Properties of References



- Accurate
- Temperature Stable
- Time Stable
- Insensitive to V_{BIAS}
- Low Output Impedance (voltage reference)
- Floating
- Small Area
- Low Power Dissipation
- Process Tolerant
- Process Transportable

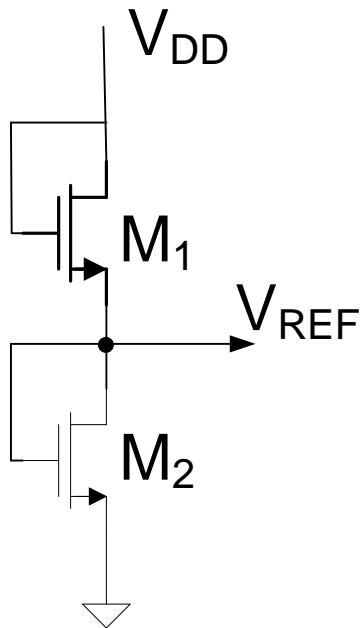
Desired Properties of References



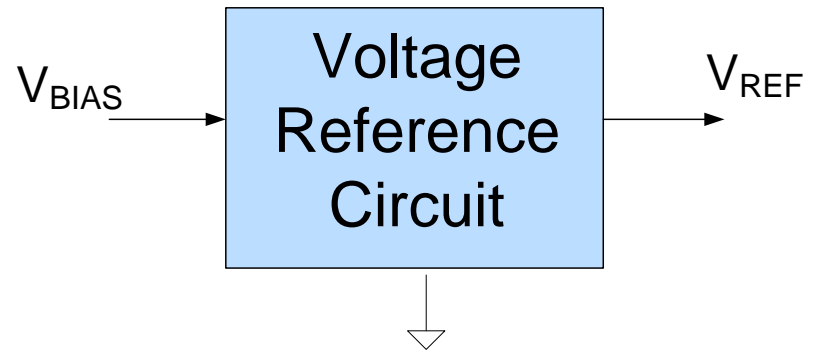
- Accurate ✓
- Temperature Stable ✓
- Time Stable ✓
- Insensitive to V_{BIAS} ✓
- Low Output Impedance (voltage reference)
- Floating
- Small Area
- Low Power Dissipation
- Process Tolerant ✓
- Process Transportable

Similar properties desired in other references

Consider Voltage References



Popular Voltage “Reference”



$$I_{D1} = \frac{\mu C_{OX} W_1}{2L_1} (V_{GS1} - V_{T1})^2$$

$$I_{D2} = \frac{\mu C_{OX} W_2}{2L_2} (V_{GS2} - V_{T2})^2$$

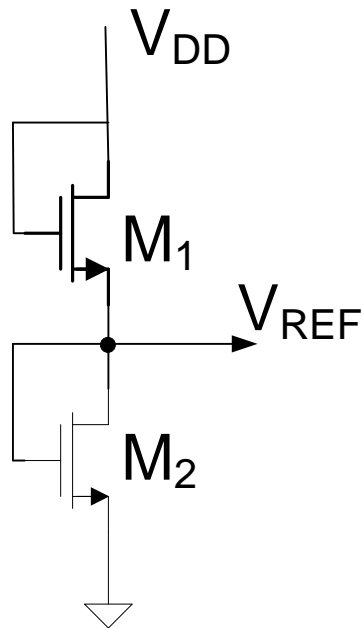
$$V_{T1} = V_{T0} + \gamma (\sqrt{\phi + V_{REF}} - \sqrt{\phi})$$

$$V_{DD} - V_{REF} - V_{T1} = \sqrt{\frac{W_2 L_1}{W_1 L_2}} (V_{REF} - V_{T2})$$

If matching assumed and γ effects neglected

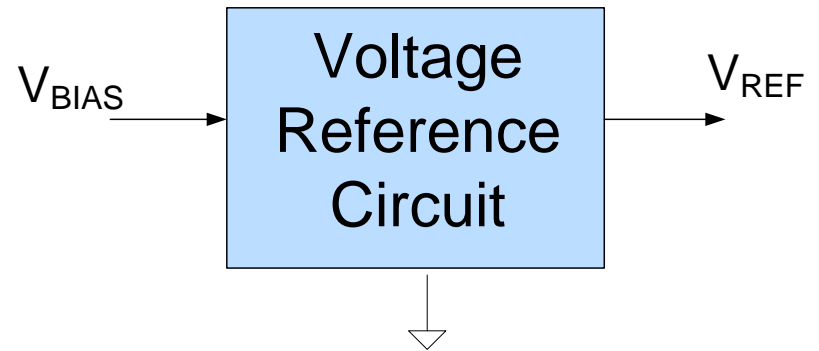
$$V_{REF} = \frac{V_{DD} - V_{T0} \left(1 - \sqrt{\frac{W_2 L_1}{W_1 L_2}} \right)}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}}$$

Consider Voltage References



Popular Voltage “Reference”

Uses as a reference limited to biasing and even for this may not be good enough !



If matching assumed and γ effects neglected

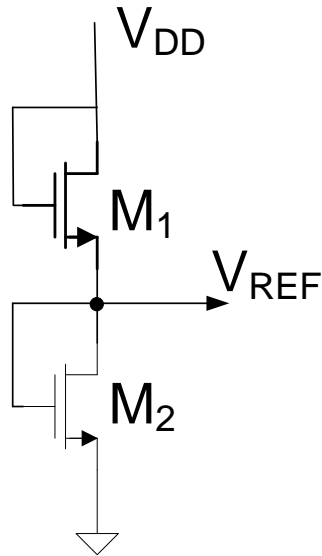
$$V_{REF} = \frac{V_{DD} - V_{T0} \left(1 - \sqrt{\frac{W_2 L_1}{W_1 L_2}} \right)}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}}$$

Dependent upon V_{DD} , V_{T0} , matching, process variations, γ

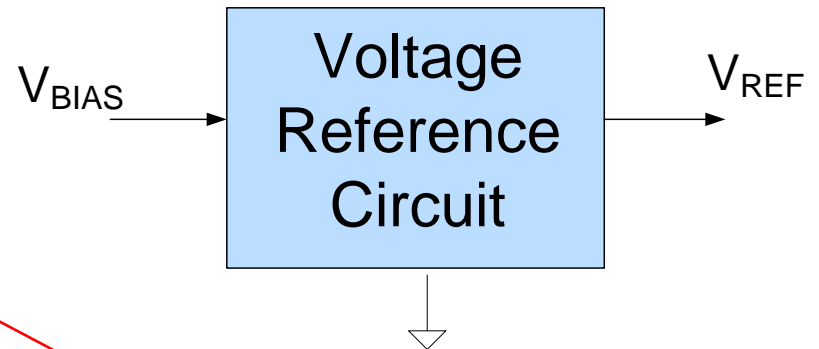
Termed a V_{DD}, V_{TH} reference

Does not satisfy key properties of voltage references

Consider Voltage References



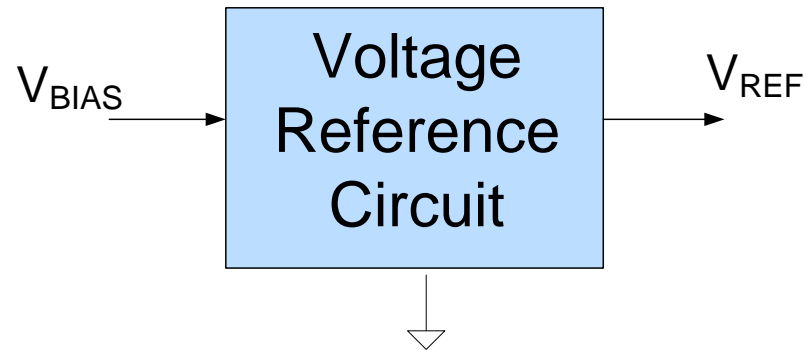
V_{DD}, V_T reference



$$V_{REF} = \frac{V_{DD} - V_{T0} \left(1 - \sqrt{\frac{W_2 L_1}{W_1 L_2}} \right)}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}}$$

Observation – Variables with units Volts needed to build any voltage reference

Voltage References



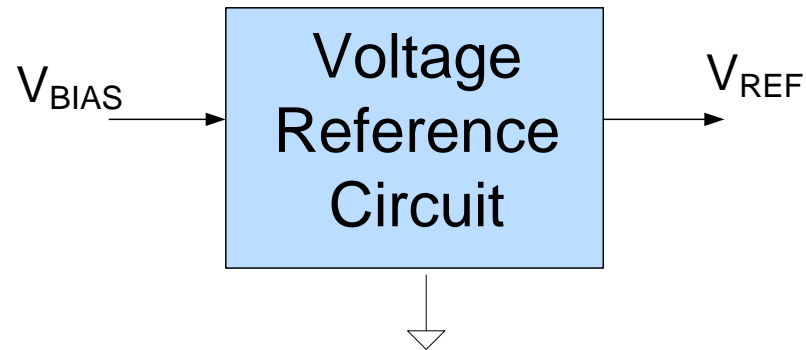
Observation – Variables with units Volts needed to build any voltage reference

What variables available in a process have units volts?

What variables which have units volts satisfy the desired properties of a voltage reference?

How can a circuit be designed that “expresses” the desired variables?

Voltage References



Observation – Variables with units Volts needed to build any voltage reference

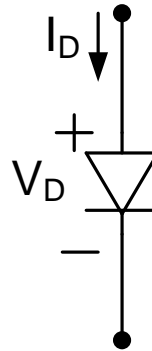
What variables available in a process have units volts?

V_{DD} , V_T , V_D (diode), V_Z , V_{BE} , V_t , V_{TH} ???

What variables which have units volts satisfy the desired properties of a voltage reference?

How can a circuit be designed that “expresses” the desired variables?

Voltage References



Consider the Diode

$$I_D = J_S A e^{\frac{V_D}{V_t}}$$

$$J_S = \tilde{J}_{SX} \left[T^m e^{\frac{-V_{G0}}{V_t}} \right]$$

$$V_t = \frac{kT}{q}$$

$$\frac{k}{q} = \frac{1.38 \times 10^{-23} \text{ V}}{1.602 \times 10^{-19}} \text{ } ^\circ\text{K} = 8.614 \times 10^{-5} \frac{\text{V}}{^\circ\text{K}}$$

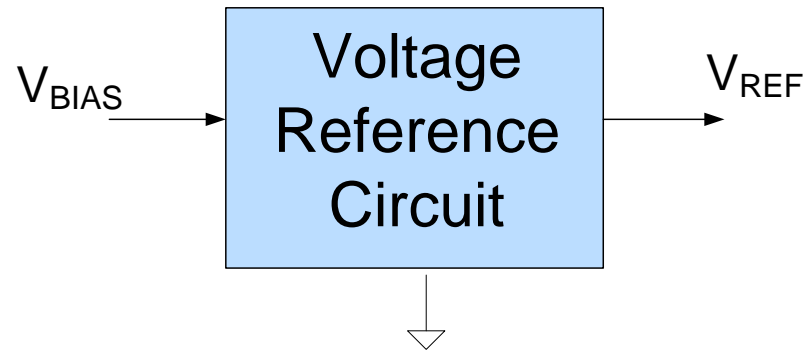
$$V_{G0} = 1.206\text{V}$$

termed the bandgap voltage

pn junction characteristics highly temperature dependent through both the exponent and J_S

V_{G0} is nearly independent of process and temperature

Voltage References



Observation – Variables with units Volts needed to build any voltage reference

What variables available in a process have units volts?

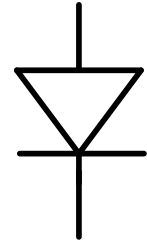
V_{DD} , V_T , V_D (diode), V_Z , V_{BE} , V_t , V_{G0} ???

What variables which have units volts satisfy the desired properties of a voltage reference? V_{G0} and ??

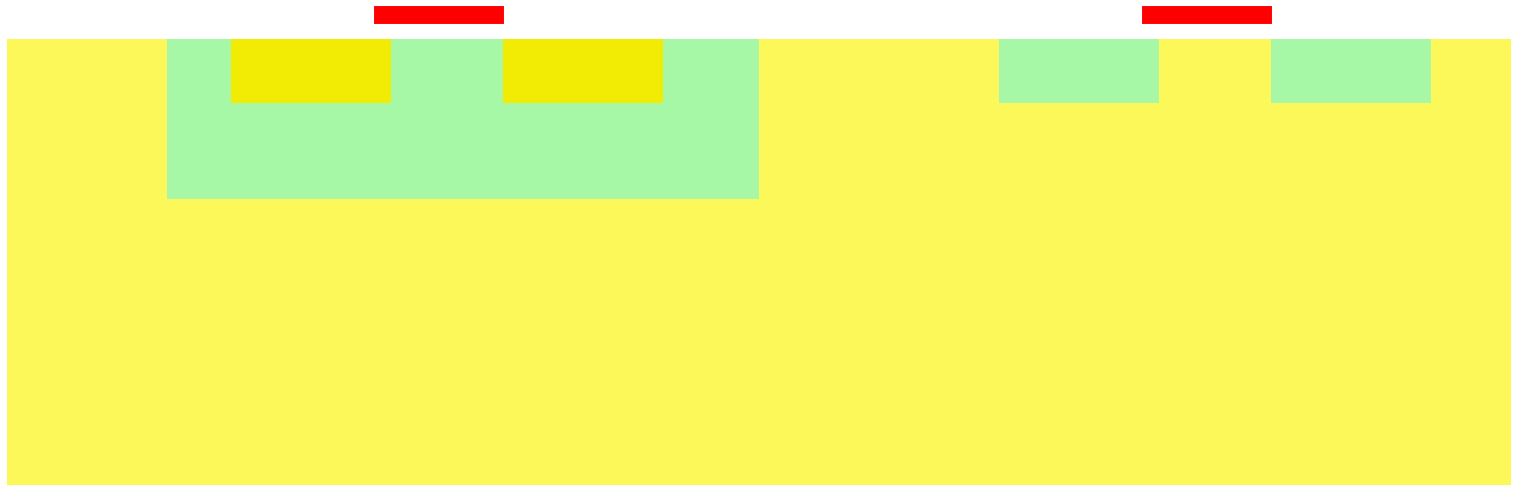
How can a circuit be designed that “expresses” the desired variables?

V_{G0} is deeply embedded in a device model with horrible temperature effects !
Good diodes are not widely available in most MOS processes !

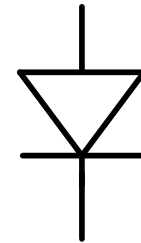
Voltage References



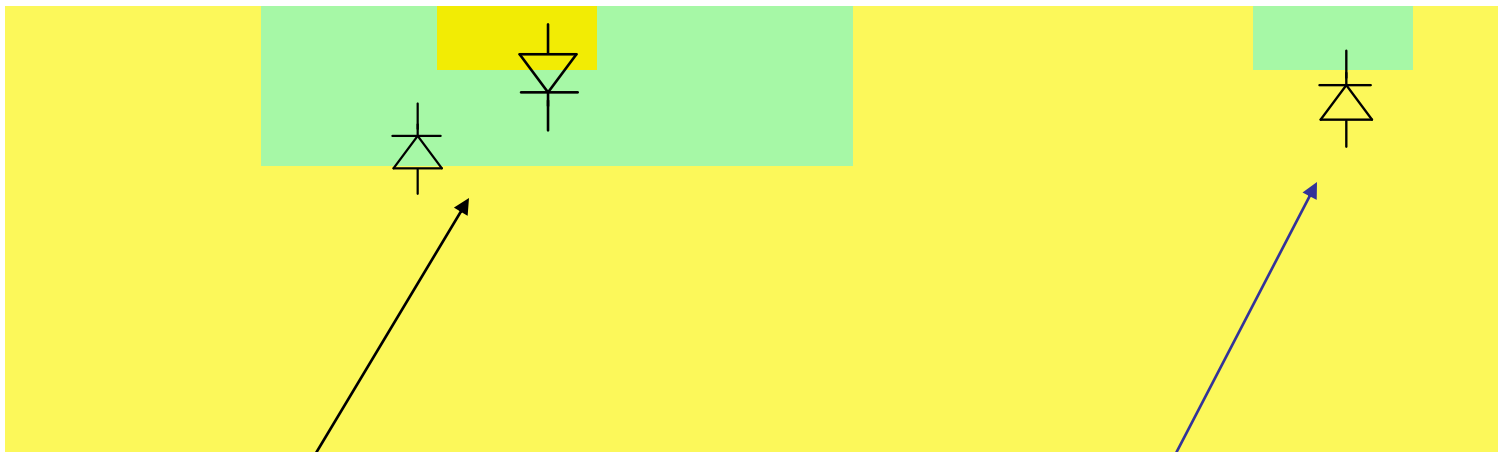
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Voltage References



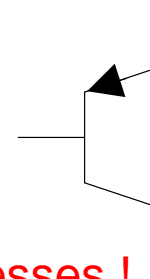
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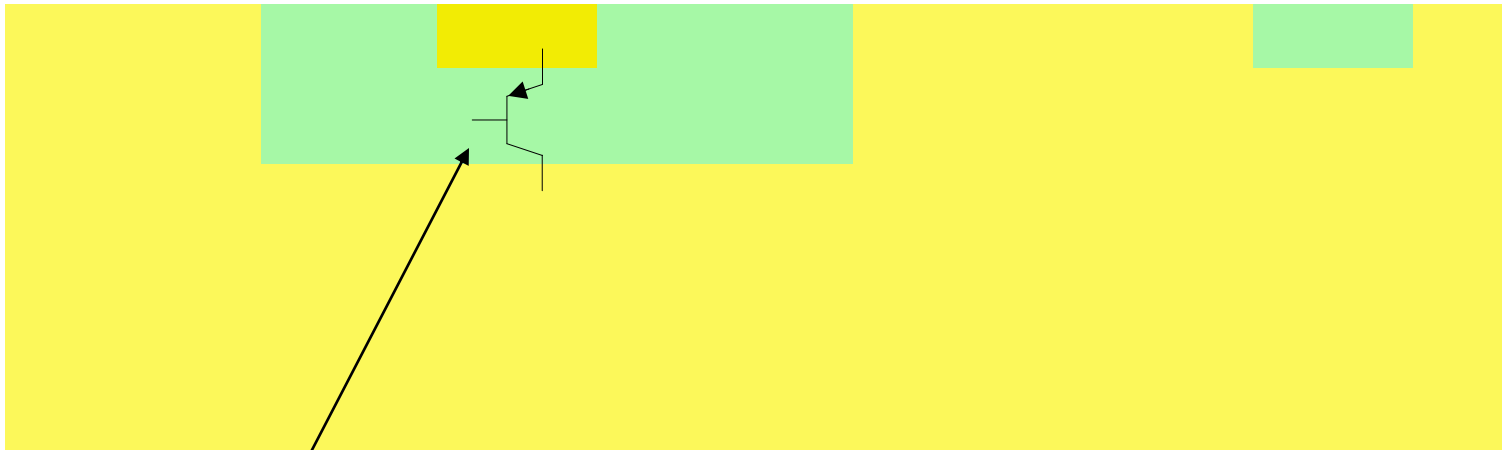
These diodes interact and actually form substrate pnp transistor

Not practical to forward bias junction

Voltage References

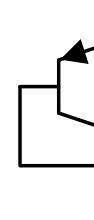


Good diodes are not widely available in most MOS processes !

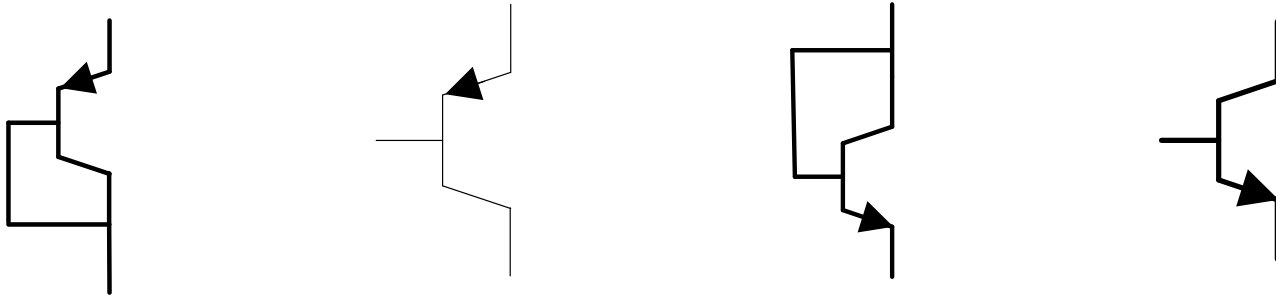


Substrate pnp transistor

Diode-connected
substrate pnp



Voltage References



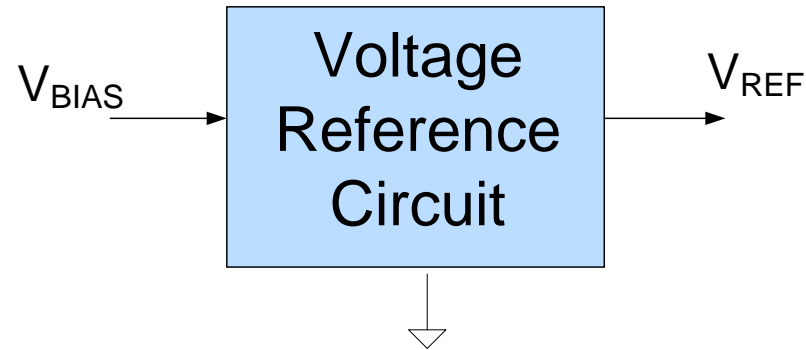
$$I_C = J_S A e^{\frac{V_{BE}}{V_t}}$$

$$J_S = \tilde{J}_{SX} \left[T^m e^{\frac{-V_{G0}}{V_t}} \right]$$

Bandgap Voltage Appears in BJT Model Equation as well

$$I_C(T) = \left(\tilde{J}_{SX} A \left[T^m e^{\frac{-V_{G0}}{V_t}} \right] \right) e^{\frac{V_{BE}(T)}{V_t}}$$

Voltage References

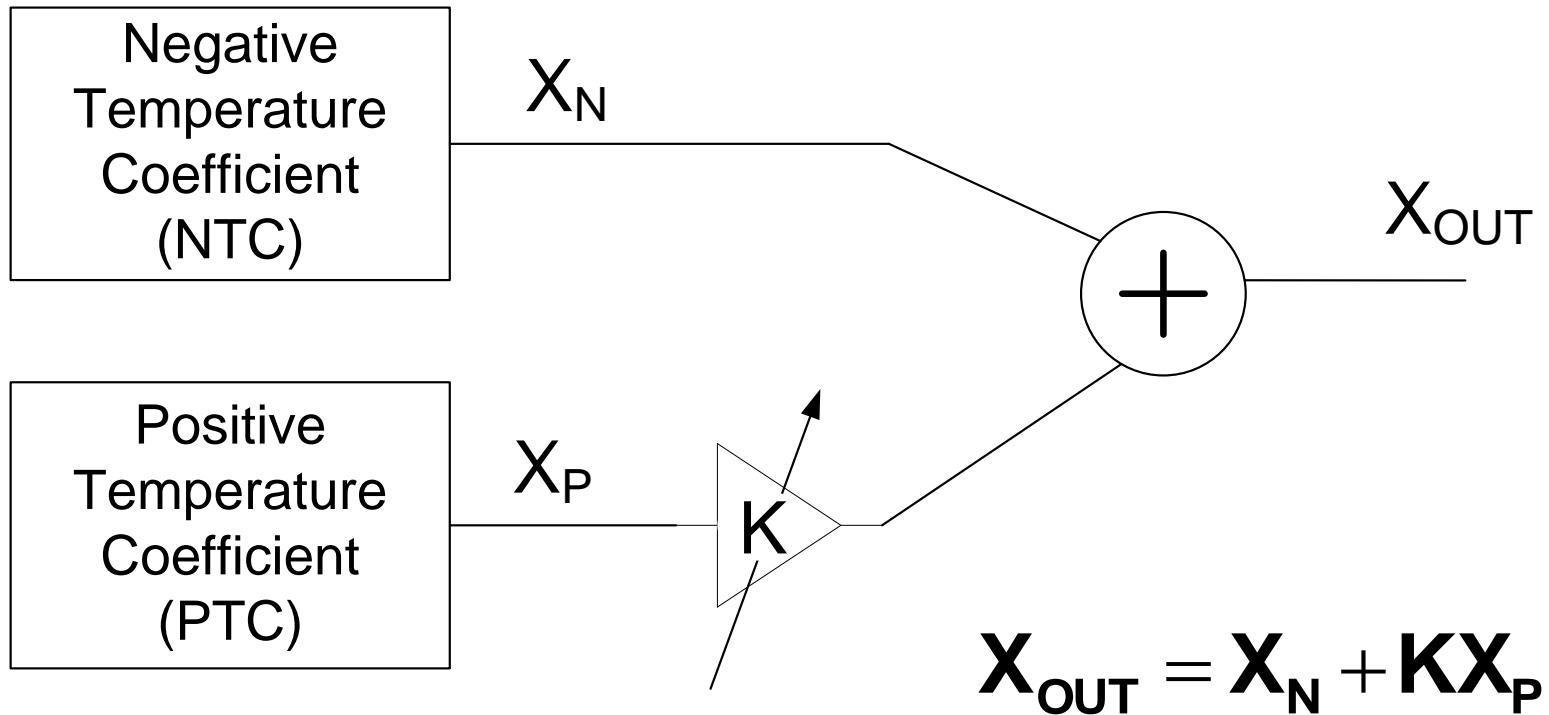


Voltage references that “express” the bandgap voltage are termed “Bandgap References”

V_{G0} is deeply embedded in a device model with horrible temperature effects !

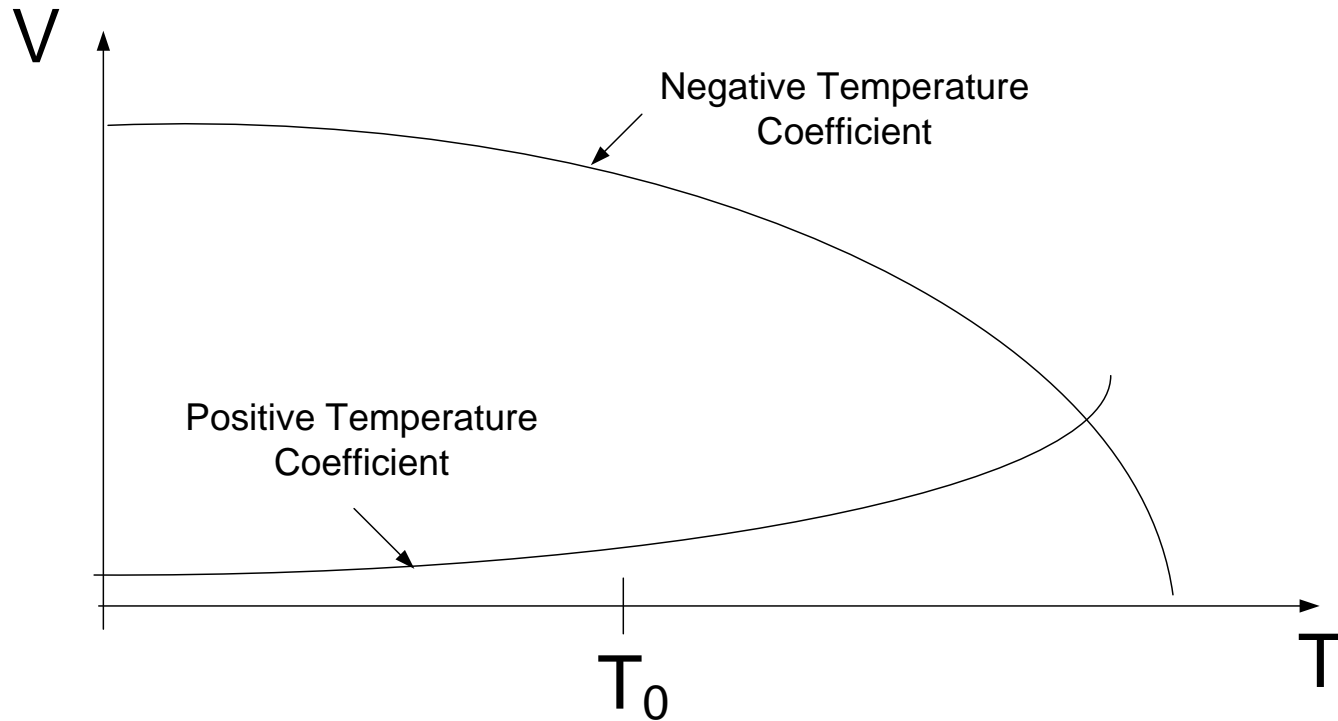
Good BJTs are not widely available in most MOS processes but the substrate pnp is available !

Standard Approach to Building Voltage References

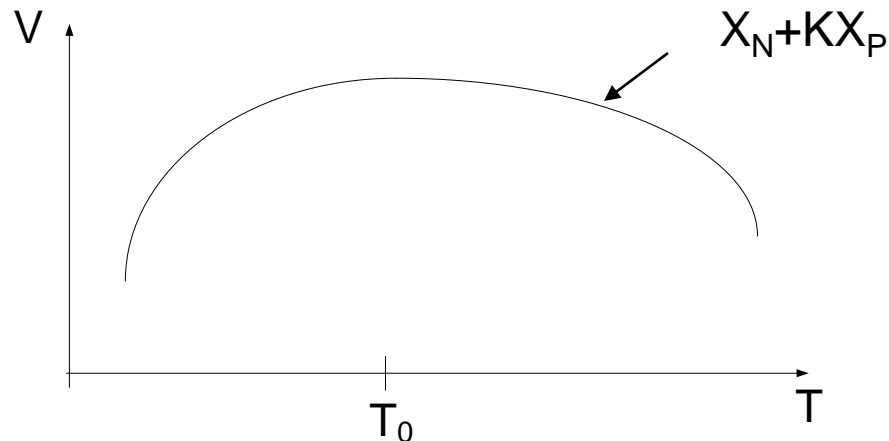
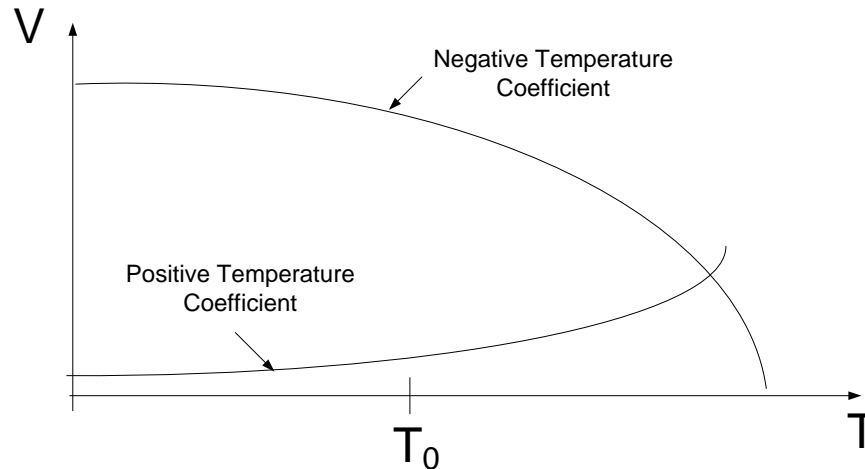


Pick K so that at some temperature T_0 , $\left. \frac{\partial(X_N + KX_P)}{\partial T} \right|_{T=T_0} = 0$

Standard Approach to Building Voltage References



Standard Approach to Building Voltage References



Select K so that

$$\left. \frac{\partial (X_N + KX_P)}{\partial T} \right|_{T=T_0} = 0$$

Bandgap Voltage References

Consider two BJTs (or diodes)



$$I_C(T) = \left(\tilde{I}_{SX} \left[T^m e^{\frac{-V_{G0}}{V_t}} \right] \right) e^{\frac{V_{BE}(T)}{V_t}}$$

$$V_{BE} = V_{G0} + V_t \ln \left(\frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T$$

$$V_{BE2} - V_{BE1} = \Delta V_{BE} = \left[\frac{k}{q} \ln \left(\frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right) \right] T$$

If the $\frac{I_{C2} A_{E1}}{I_{C1} A_{E2}}$ ratio is constant and >1 , the TC of ΔV_{BE} is positive

ΔV_{BE} is termed a PTAT voltage (Proportional to Absolute Temperature)

This relationship applies irrespective of how temperature dependent I_{C1} and I_{C2} may be provided the ratio is constant !!

Bandgap Voltage References

Consider two BJTs (or diodes)



$$V_{BE2} - V_{BE1} = \Delta V_{BE} = \left[\frac{k}{q} \ln \left(\frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right) \right] T$$

$$\frac{\partial (V_{BE2} - V_{BE1})}{\partial T} = \frac{k}{q} \ln \left(\frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right)$$

At room temperature if $\ln \left(\frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right) = 1$

$$V_{BE2} - V_{BE1} = [8.6 \times 10^{-5} \times 300] = 25.8 \text{ mV}$$

and

$$\left. \frac{\partial (V_{BE2} - V_{BE1})}{\partial T} \right|_{T=T_0=300^\circ\text{K}} = 8.6 \times 10^{-5} = 86 \mu\text{V}/^\circ\text{C}$$

The temperature coefficient of the PTAT voltage is rather small

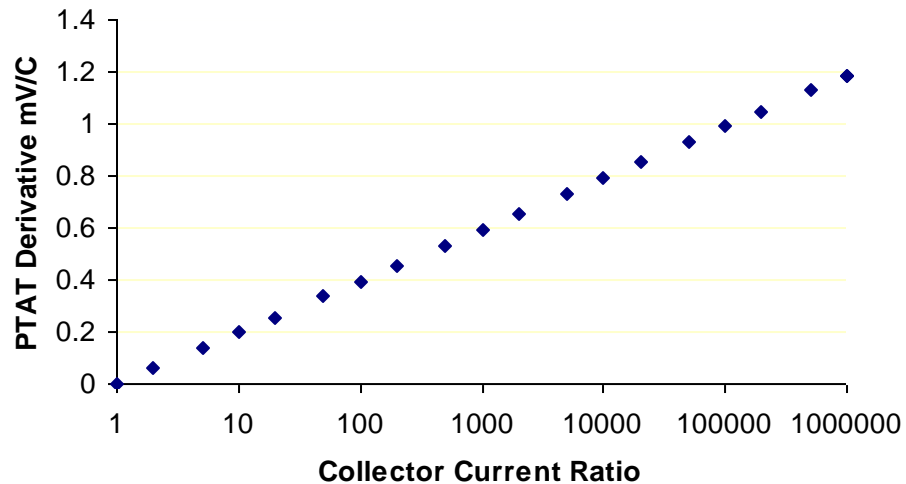
Bandgap Voltage References

Consider two BJTs (or diodes)



$$\frac{\partial(V_{BE2} - V_{BE1})}{\partial T} = \frac{k}{q} \ln\left(\frac{I_{C2}}{I_{C1}}\right)$$

At room temperature if $A_{E1} = A_{E2}$



The temperature coefficient of the PTAT voltage is rather small even if large collector current ratios are used

Bandgap Voltage References

Consider two BJTs (or diodes)

Assume $m=2.3$, $V_{G0}=1.2V$



$$I_C(T) = \left(\tilde{J}_{SX} A_E \left[T^m e^{\frac{-V_{G0}}{V_t}} \right] \right) e^{\frac{V_{BE}(T)}{V_t}}$$

$$V_{BE} = V_{G0} + V_t \ln \left(\frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T$$

If I_C is independent of temperature, it follows that

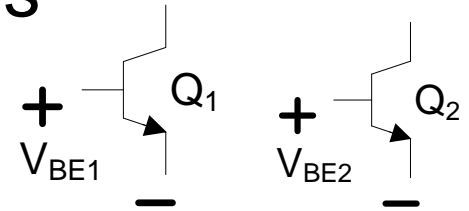
$$\frac{\partial V_{BE}}{\partial T} = \frac{k}{q} \left[-m + \left(\frac{V_{BE} - V_{G0}}{V_t} \right) \right]$$

$$\left. \frac{\partial V_{BE}}{\partial T} \right|_{T=T_0=300^\circ K} \cong 8.6 \times 10^{-5} \left[-2.3 + \left(\frac{0.65 - 1.2}{25 \text{mV}} \right) \right] \cong -2.1 \text{mV}/^\circ \text{C}$$

Bandgap Voltage References

Consider two BJTs (or diodes)

Assume $m=2.3$, $V_{G0}=1.2V$

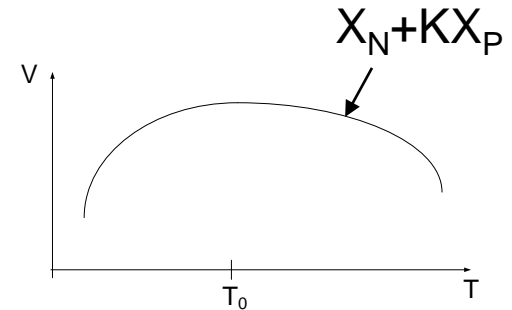


Thus if I_C independent of temperature

$$\left. \frac{\partial V_{BE}}{\partial T} \right|_{T=T_0=300^{\circ}K} \cong -2.1 \text{ mV}/^{\circ}\text{C}$$

And if $\ln\left(\frac{I_{C2} A_{E1}}{I_{C1} A_{E2}}\right) = 1$

$$\left. \frac{\partial (V_{BE2} - V_{BE1})}{\partial T} \right|_{T=T_0=300^{\circ}K} = 86 \mu\text{V}/^{\circ}\text{C}$$



Magnitude of TC of PTAT source is much smaller than that of V_{BE} source

Define:

$$X_N = V_{BE} \quad X_P = V_{BE2} - V_{BE1}$$

Create circuit with:

$$X_{OUT} = X_N + KX_P$$

If we want $\left. \frac{\partial (X_N + KX_P)}{\partial T} \right|_{T=T_0} = 0$

K will need to be large

Bandgap Voltage References

Consider two BJTs (or diodes)



It was just shown that if I_C is independent of temperature

$$\left. \frac{\partial V_{BE}}{\partial T} \right|_{T=T_0=300^\circ\text{K}} \cong 8.6 \times 10^{-5} \left[-2.3 + \left(\frac{0.65 - 1.2}{25\text{mV}} \right) \right] \cong -2.1 \text{mV}/^\circ\text{C}$$

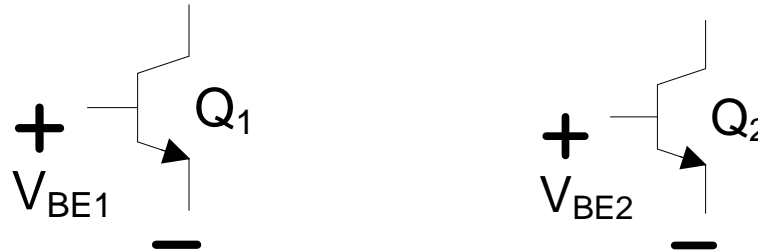
If I_C is reasonably independent of temperature, V_{BE} will still provide a negative TC

$$V_{BE} = V_{G0} + V_t \ln \left(\frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T$$

Even if I_C is highly dependent on temperature, V_{BE} will still provide a negative TC

Bandgap Voltage References

Consider two BJTs (or diodes)

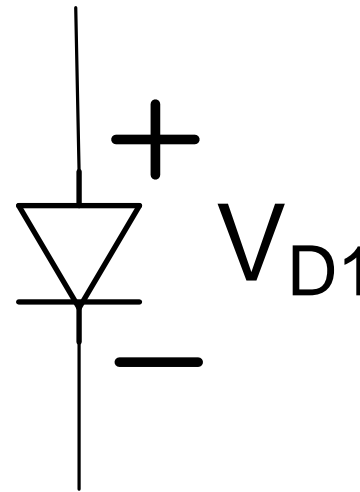
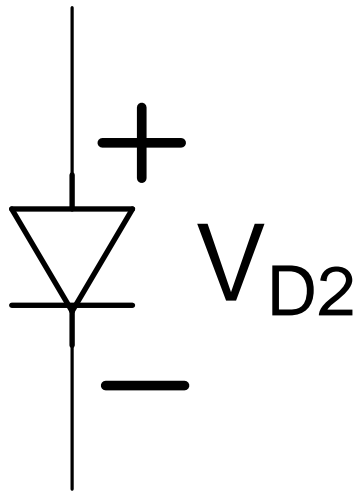


Key observation about diodes and diode-connected BJTs

1. If ratio of currents in two devices is constant, ΔV_{BE} is PTAT independent of the temperature dependence of the currents and sensitivity is small
2. V_{BE} has a negative temperature coefficient for a wide range of temperature dependent or temperature independent currents and sensitivity is much larger than that of ΔV_{BE}

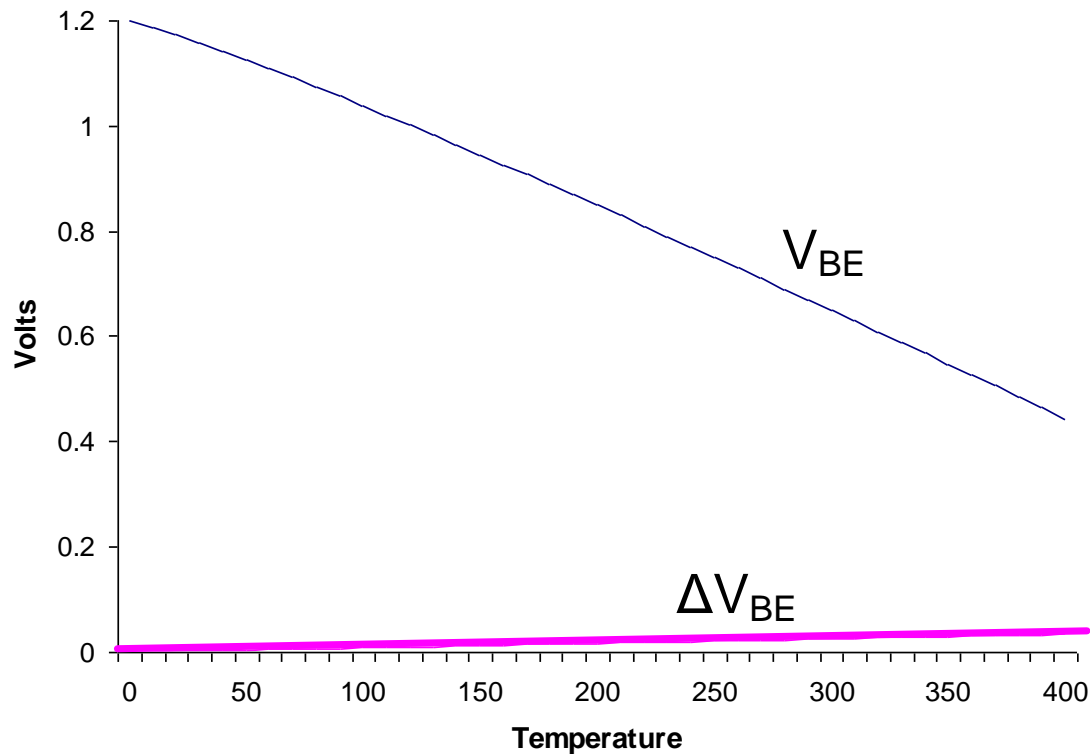
Bandgap Reference Circuits

- Circuits that implement ΔV_{BE} and V_{BE} or ΔV_D and V_D widely used to build bandgap references

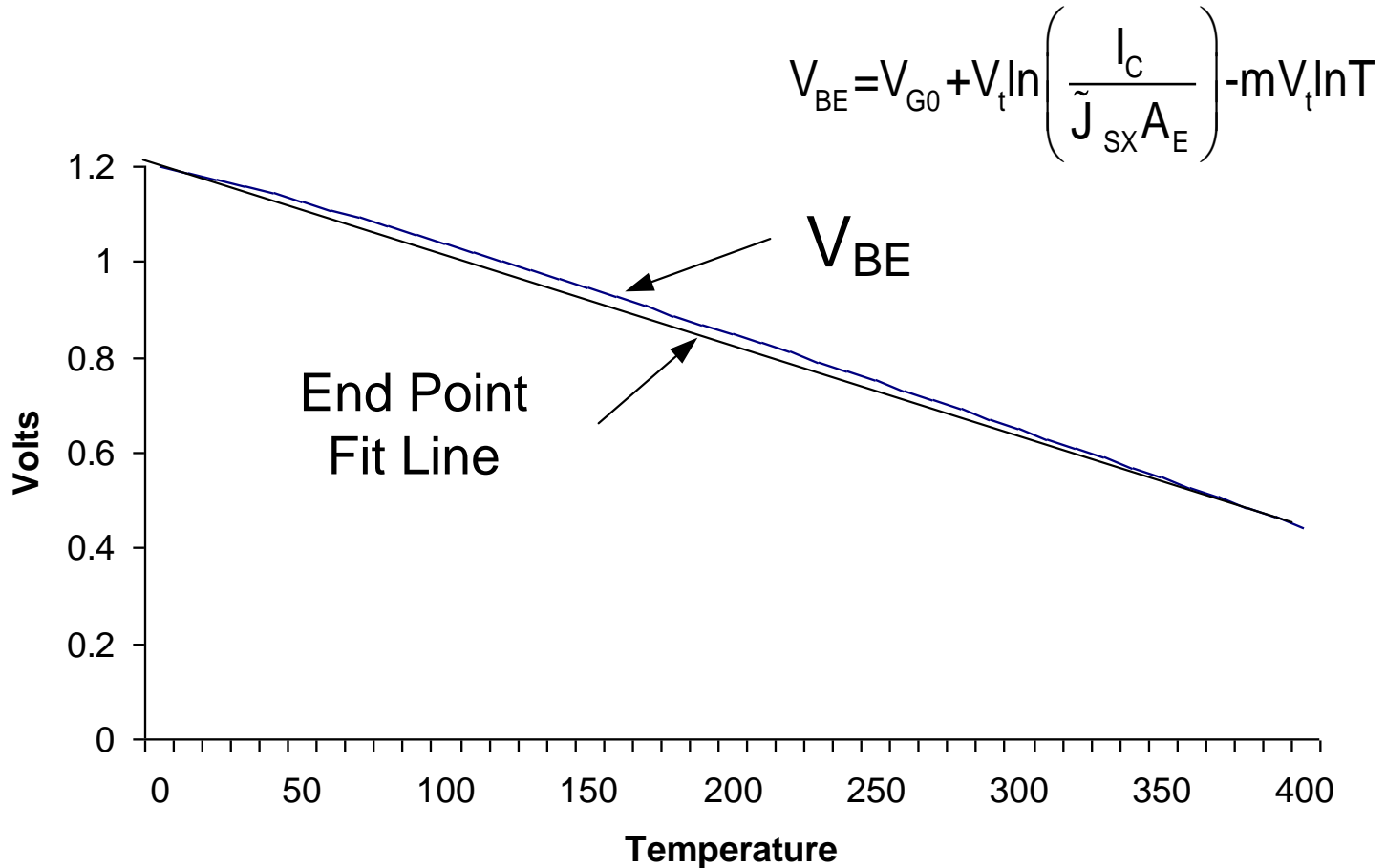


V_{BE} and ΔV_{BE} with constant I_C

$$V_{BE} = V_{G0} + V_t \ln \left(\frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T$$

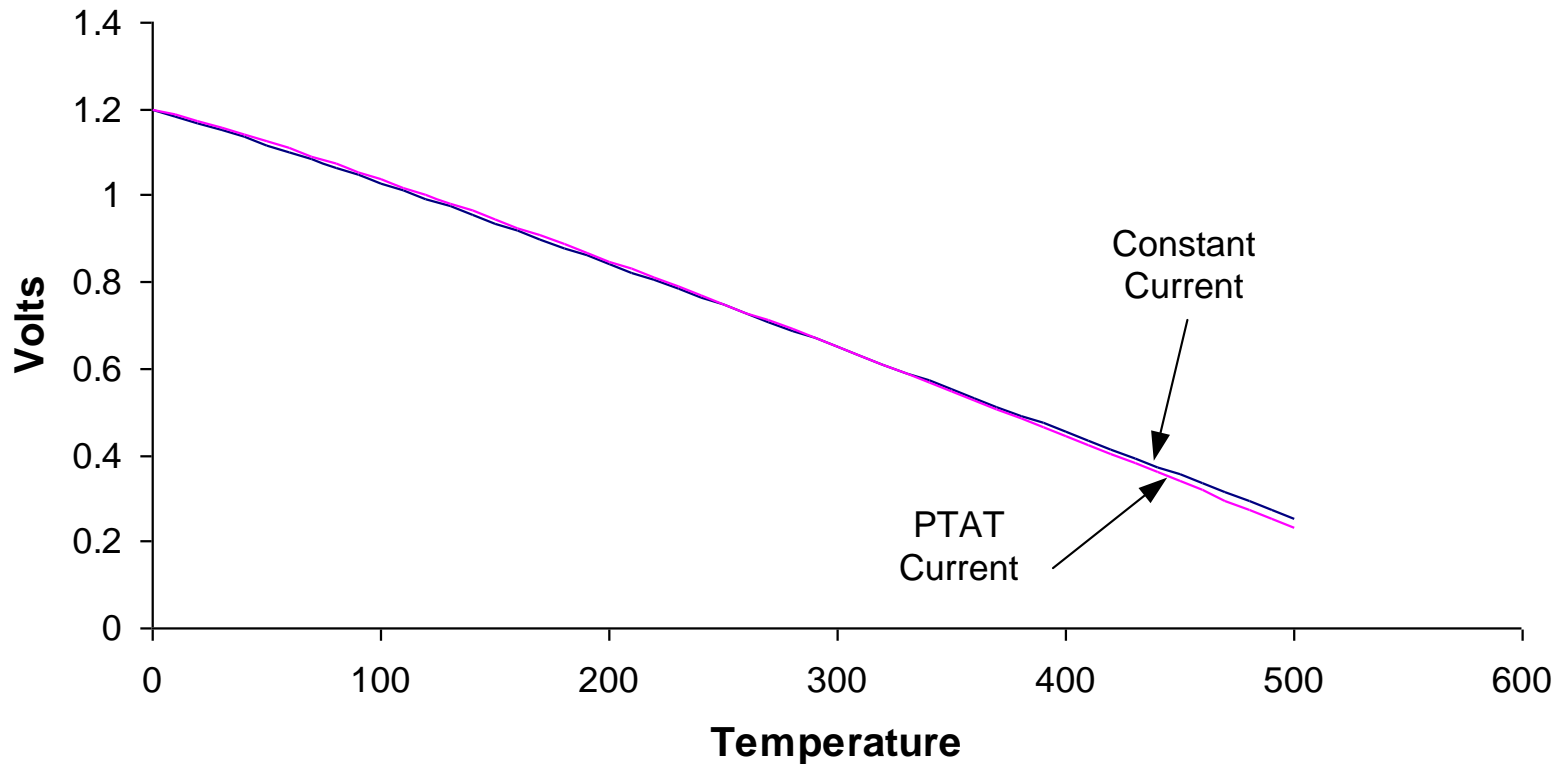


V_{BE} plot for constant I_C



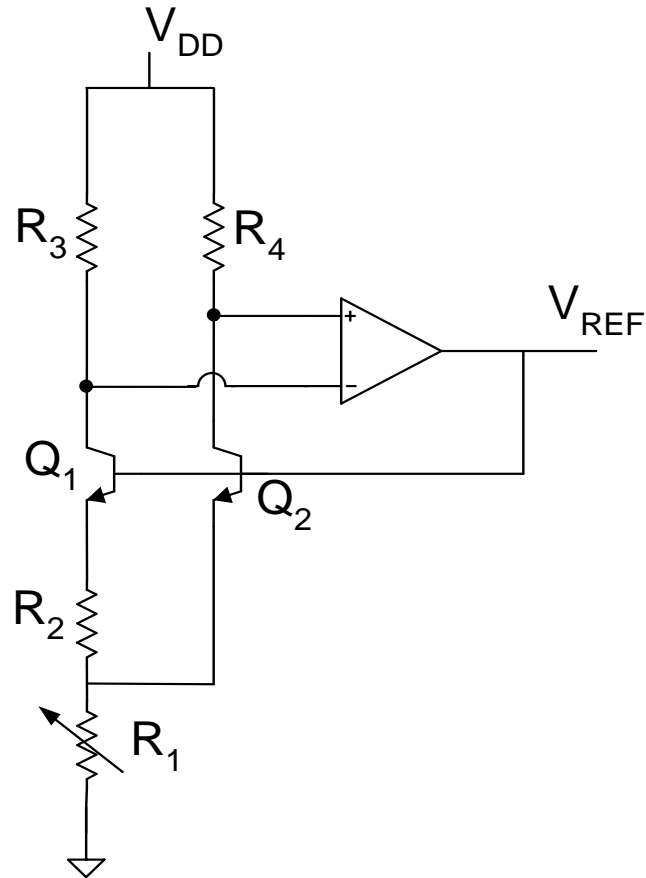
Combined effects of the T and $T \ln T$ terms in V_{BE} is nearly linear dependent on T

Comparison of V_{BE} with constant current and PTAT current



Even if I_C is highly-dependent on current, temperature dependence of V_{BE} is still nearly linearly dependent upon T

First Bandgap Reference (and still widely used!)



P.Brokaw, "A Simple Three-Terminal IC Bandgap Reference", IEEE Journal of Solid State Circuits, Vol. 9, pp. 388-393, Dec. 1974.

- Brokaw coined term "bandgap reference" when referring to this circuit
- Properties very similar to a circuit introduced by Widlar a small while earlier

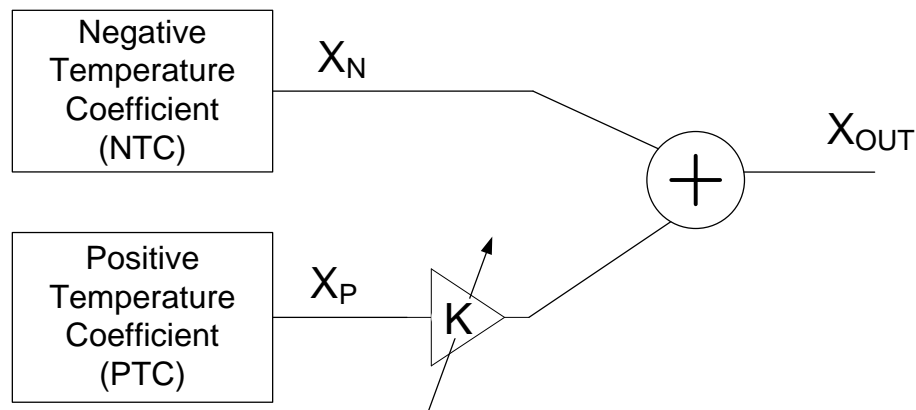
Most Published Analysis of Bandgap Circuits

V_{REF} often expressed as:

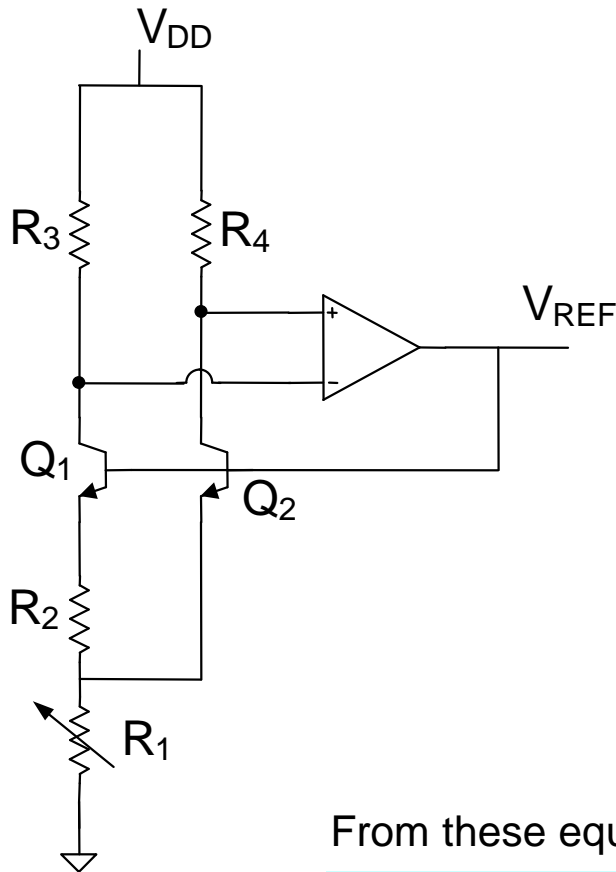
$$V_{REF} = V_{G0} + \frac{T}{T_0} (V_{BE0} - V_{G0}) + K \frac{kT}{q} \ln\left(\frac{J_2}{J_1}\right) + (m-1) \frac{kT}{q} \ln\left(\frac{T_0}{T}\right)$$

where K is the gain of the PTAT signal

(Not a solution and dependent upon both T_0 and V_{BE0})



First Bandgap Reference (and still widely used!)



$$I_{E1} R_2 + V_{BE1} = V_{BE2}$$

$$V_{REF} = V_{BE2} + (I_{E1} + I_{E2}) R_1$$

$$I_{C1} = \frac{V_{DD} - V_{C2}}{R_3}$$

$$I_{C2} = \frac{V_{DD} - V_{C2}}{R_4}$$

$$I_{C1} = \alpha_1 I_{E1}$$

$$I_{C2} = \alpha_2 I_{E2}$$

$$I_{E1} = I_{E2} \left[\frac{\alpha_2 R_4}{\alpha_1 R_3} \right] \rightarrow I_{C1} = I_{C2} \left[\frac{R_4}{R_3} \right]$$

$$\alpha = \frac{\beta}{1 + \beta}$$

From these equations can show

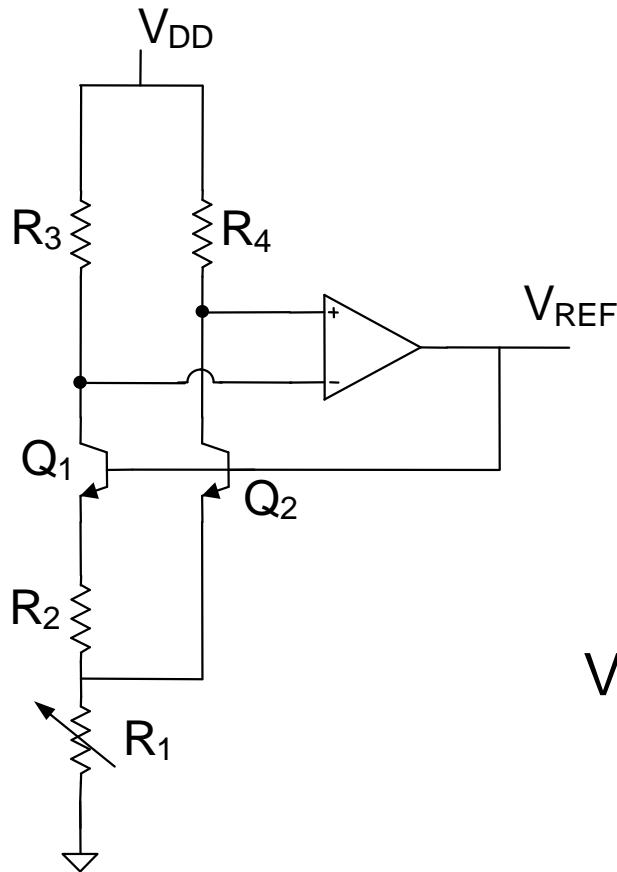
$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[\frac{R_1}{R_2} \left(1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$

Not a solution but can provide zero temp slope by adjusting R_1

First Bandgap Reference (and still widely used!)

Will now obtain solution for V_{REF} (in terms of component values and model parameters)

$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[\frac{R_1}{R_2} \left(1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$



$$V_{BE1} = V_{G0} + V_t \ln \left(\frac{I_{C1}}{\tilde{J}_{SX} A_{E1}} \right) - m V_t \ln T$$

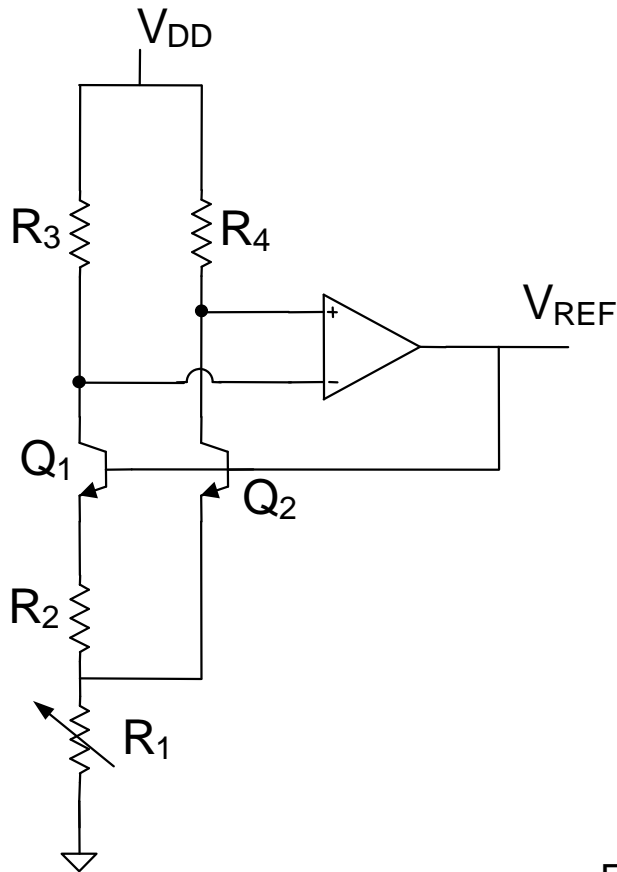
$$V_{BE2} = V_{G0} + V_t \ln \left(\frac{I_{C2}}{\tilde{J}_{SX} A_{E2}} \right) - m V_t \ln T$$

$$I_{C1} = I_{C2} \left[\frac{R_4}{R_3} \right]$$

$$V_{BE2} - V_{BE1} = \Delta V_{BE} = \left[\frac{k}{q} \ln \left(\frac{A_{E1}}{A_{E2}} \left[\frac{R_3}{R_4} \right] \right) \right] T$$

First Bandgap Reference (and still widely used!)

Will now obtain solution for V_{REF} (in terms of component values and model parameters)



$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[\frac{R_1}{R_2} \left(1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$

$$\left. \begin{aligned} V_{BE1} &= V_{G0} + V_t \ln \left(\frac{I_{C1}}{\tilde{J}_{SX} A_{E1}} \right) - m V_t \ln T \\ V_{BE2} &= V_{G0} + V_t \ln \left(\frac{I_{C2}}{\tilde{J}_{SX} A_{E2}} \right) - m V_t \ln T \end{aligned} \right\}$$

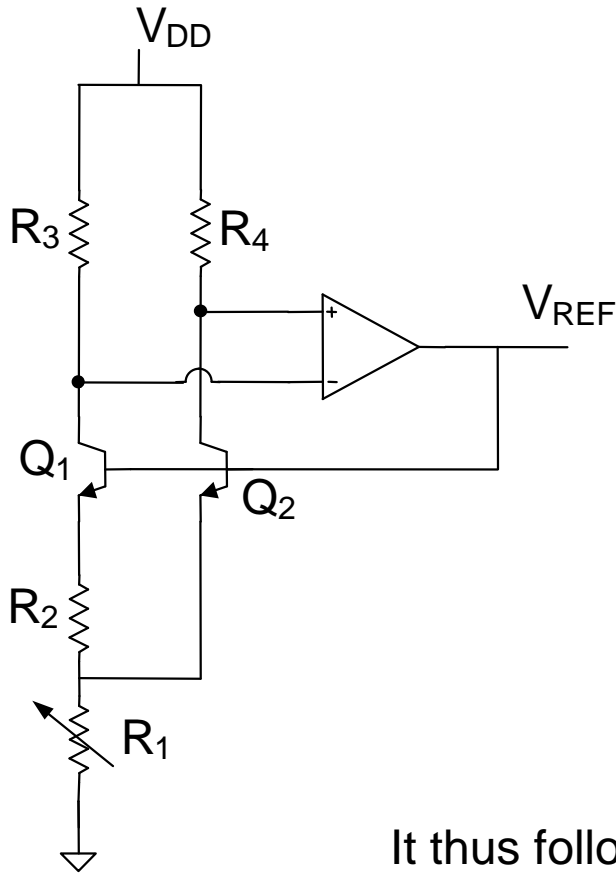
$$I_{C1} = I_{C2} \left[\frac{R_4}{R_3} \right]$$

$$\frac{I_{C1}}{\alpha_1} R_2 + V_{BE1} = V_{BE2}$$

From the expression for V_{BE2} and some routine but tedious manipulations it follows that

$$V_{BE2} = V_{G0} + (1-m) V_t \ln T + V_t \ln \left(\frac{k}{q} \frac{\alpha_1}{R_2 A_{E2} \tilde{J}_{SX}} \frac{R_3}{R_4} \ln \left(\frac{A_{E1} R_3}{A_{E2} R_4} \right) \right)$$

First Bandgap Reference (and still widely used!)



$$V_{\text{REF}} = V_{\text{BE2}} + (V_{\text{BE2}} - V_{\text{BE1}}) \left[\frac{R_1}{R_2} \left(1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$

$$V_{\text{BE2}} - V_{\text{BE1}} = \left[\frac{k}{q} \ln \left(\frac{A_{\text{E1}}}{A_{\text{E2}}} \left[\frac{R_3}{R_4} \right] \right) \right] T$$

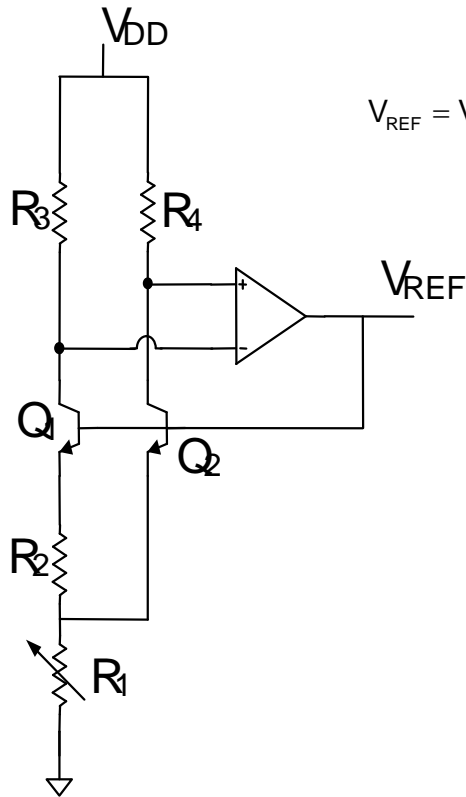
$$V_{\text{BE2}} = V_{\text{G0}} + (1-m) V_t \ln T + V_t \ln \left(\frac{k}{q R_2 A_{\text{E2}} \tilde{J}_{\text{SX}}} \frac{R_3}{R_4} \ln \left(\frac{A_{\text{E1}} R_3}{A_{\text{E2}} R_4} \right) \right)$$

It thus follows that:

$$V_{\text{REF}} = V_{\text{G0}} + V_t \ln \left\{ \frac{\alpha_1 R_3}{R_2 R_4} T \frac{k}{q} \ln \left(\frac{A_{\text{E1}} R_3}{A_{\text{E2}} R_4} \right) \right\} - V_t \left(\ln(\tilde{I}_{\text{SX2}}) + m \ln T \right) + \left[\frac{k}{q} \ln \left(\frac{A_{\text{E1}}}{A_{\text{E2}}} \left(\frac{R_3}{R_4} \right) \right) \right] \left[\frac{R_1}{R_2} \left(1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right] T$$

First Bandgap Reference (and still widely used!)

$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[\frac{R_1}{R_2} \left(1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$



$$V_{REF} = V_{G0} + V_t \ln \left\{ \frac{\alpha_1 R_3}{R_2 R_4} T \frac{k}{q} \ln \left(\frac{A_{E1} R_3}{A_{E2} R_4} \right) \right\} - V_t (\ln(\tilde{I}_{Sx2}) + m \ln T) + \left[\frac{k}{q} \ln \left(\frac{A_{E1}}{A_{E2}} \left(\frac{R_3}{R_4} \right) \right) \right] \left[\frac{R_1}{R_2} \left(1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right] T$$

This can be expressed after some manipulations as

$$V_{REF} = a_1 + b_1 T + c_1 T \ln T$$

where

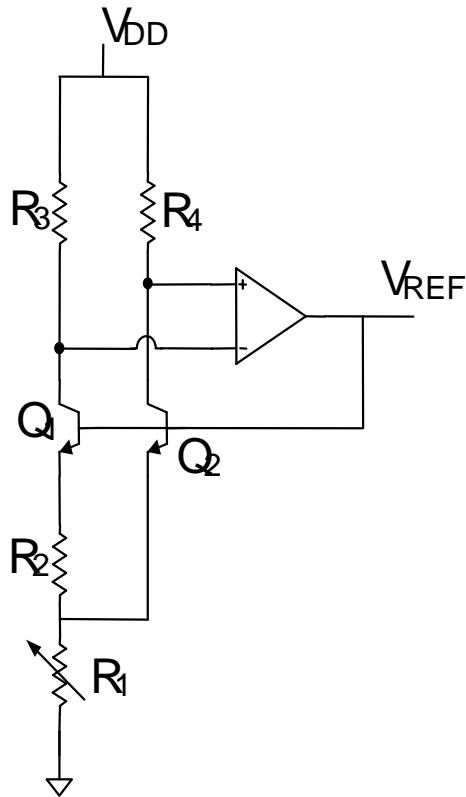
$$a_1 = V_{G0}$$

$$b_1 = \frac{k}{q} \left(\frac{R_1}{R_2} \left(1 + \frac{R_3 \alpha_1}{R_4 \alpha_2} \right) \ln \left(\frac{R_3 A_{E1}}{R_4 A_{E2}} \right) + \ln \left(\frac{k R_3}{q R_4} \alpha_1 \frac{\ln \left(\frac{R_3 A_{E1}}{R_1 A_{E2}} \right)}{\tilde{I}_{SK2} R_2} \right) \right)$$

$$c_1 = \frac{k}{q} (1 - m)$$

First Bandgap Reference (and still widely used!)

$$V_{REF} = a_1 + b_1 T + c_1 T \ln T$$



$$a_1 = V_{GO}$$

$$b_1 = \frac{k}{q} \left[\frac{R_1}{R_2} \left(1 + \frac{R_3 \alpha_1}{R_4 \alpha_2} \right) \ln \left(\frac{R_3 A_{E1}}{R_4 A_{E2}} \right) + \ln \left(\frac{k R_3 \alpha_1}{q R_4} \frac{\ln \left(\frac{R_3 A_{E1}}{R_1 A_{E2}} \right)}{\tilde{I}_{SK2} R_2} \right) \right]$$

$$c_1 = \frac{k}{q} (1 - m)$$

$$\frac{dV_{REF}}{dT} = b_1 + c_1 (1 + \ln T) = 0$$

$$T_{INF} = e^{-\left(1 + \frac{b_1}{c_1}\right)}$$

$$b_1 = -c_1 (1 + \ln T_{INF})$$

$$V_{REF} = a_1 - c_1 T_{INF}$$

$$V_{REF} = V_{GO} + \frac{k T_{INF}}{q} (m - 1)$$

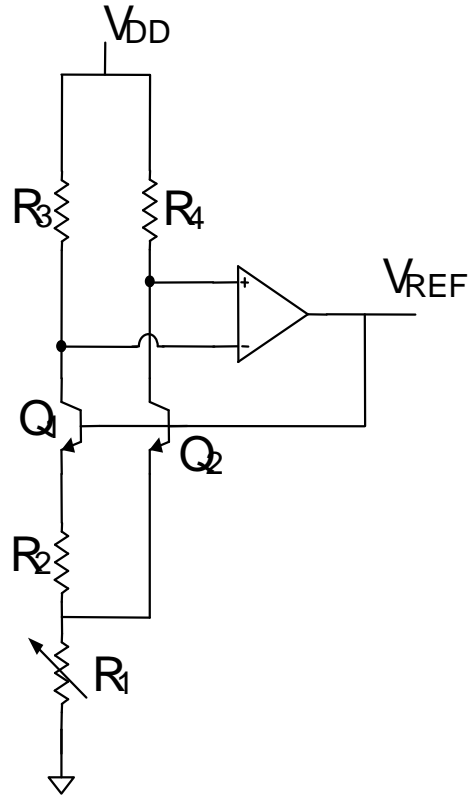
$$\frac{k T_{INF}}{q} (m - 1)$$

is small



Nearly V_{GO} output at T_{INF}

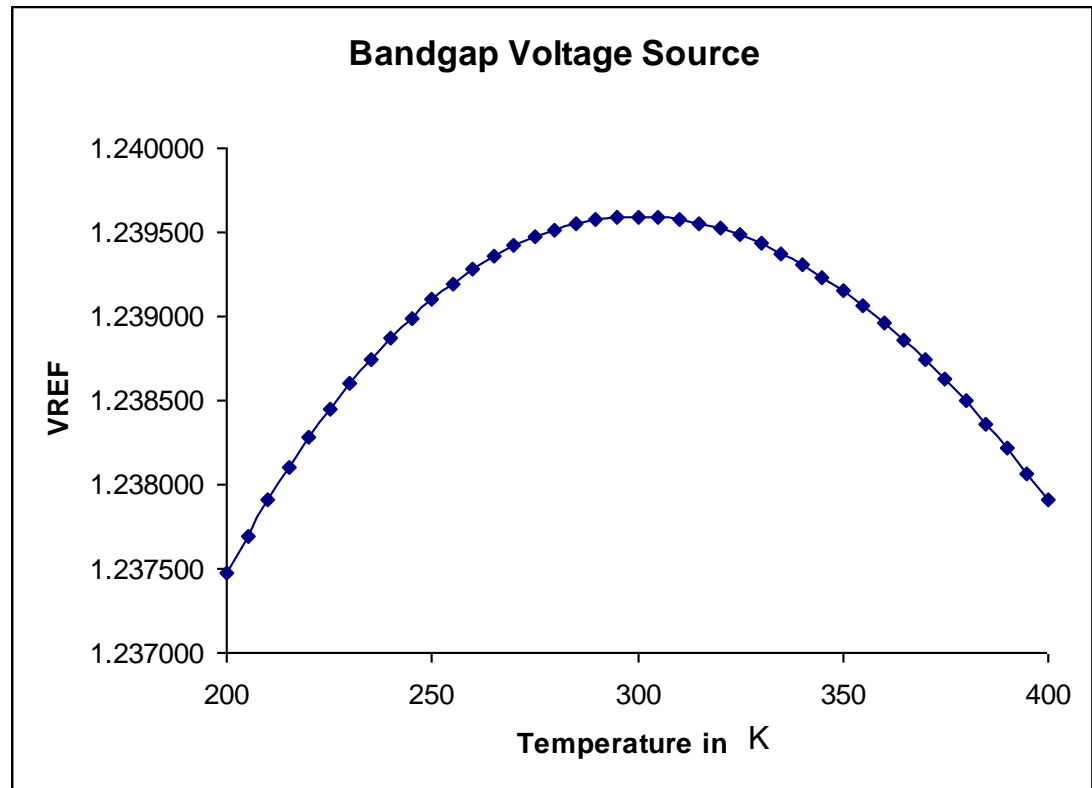
First Bandgap Reference (and still widely used!)



VGO	1.206
TO	300
VBEO2	0.65
m-1	1.3
k/q	8.61E-05

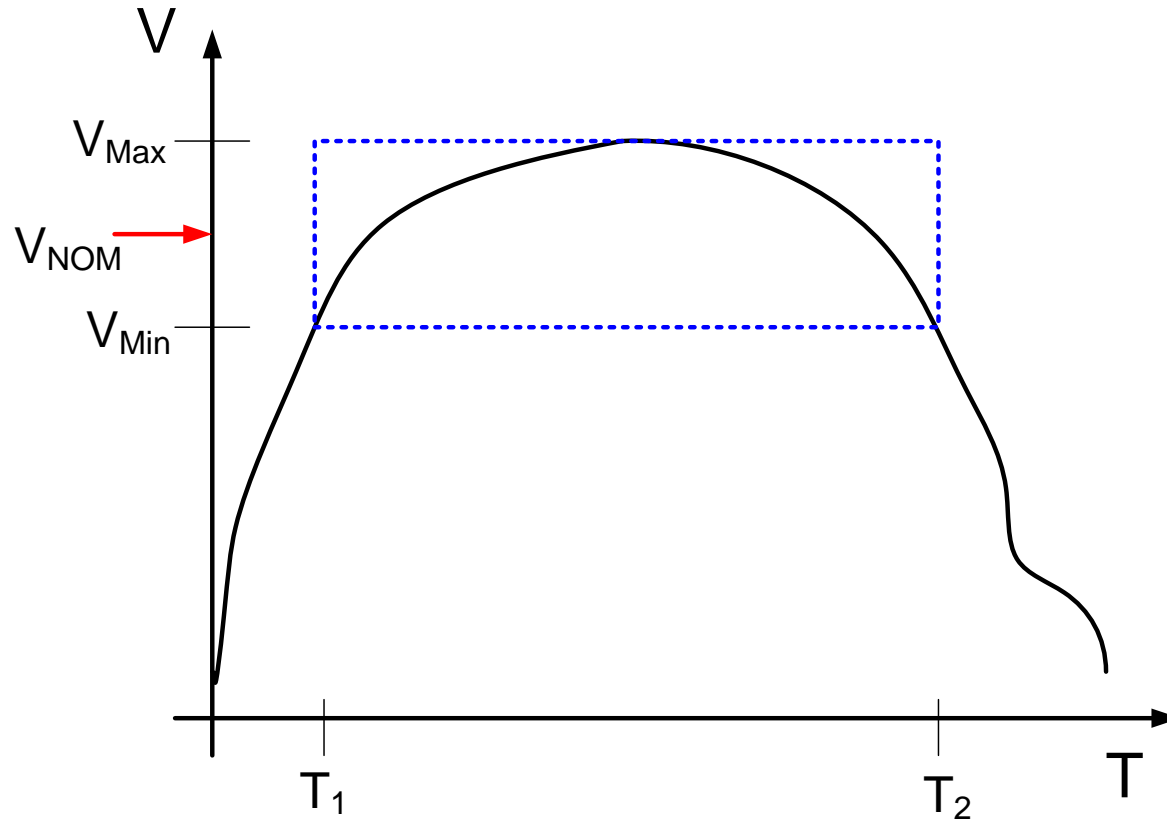
$$V_{REF} = a_1 + b_1T + c_1T \ln T$$

$$V_{REF}(T_{INF}) = V_{G0} + \frac{kT_{INF}}{q}(m-1)$$



Only 2mV change over 200°C temp range !

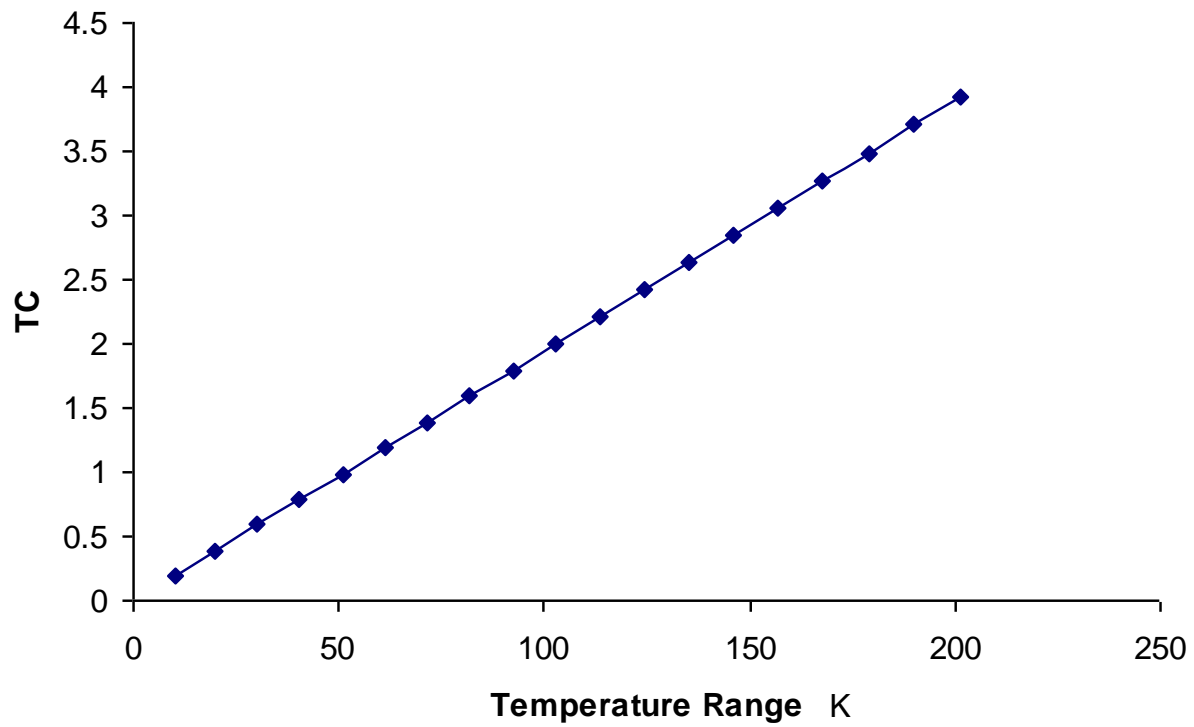
Temperature Coefficient



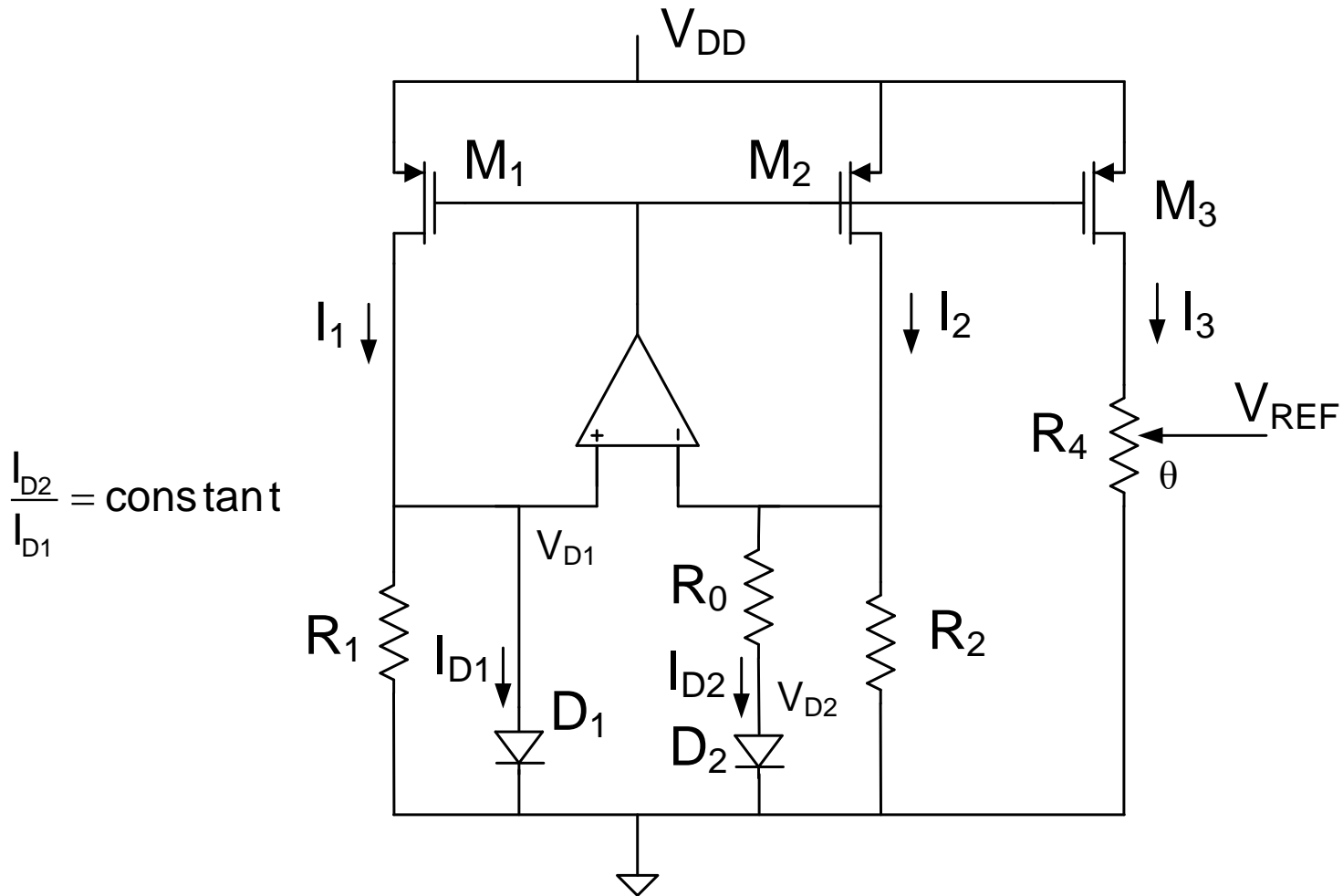
$$TC = \frac{V_{MAX} - V_{MIN}}{T_2 - T_1}$$

$$TC_{ppm} = \frac{V_{MAX} - V_{MIN}}{V_{NOM}(T_2 - T_1)} 10^6$$

TC of Bandgap Reference (+/- ppm/C)



Bamba Bandgap Reference



- [7] H. Banba, H. Shiga, A. Umezawa, T. Miyaba, T. Tanzawa, A. Atsumi, and K. Sakkui, IEEE Journal of Solid-State Circuits, Vol. 34, pp. 670-674, May 1999.

Bamba Bandgap Reference

$$I_{R0} = \frac{\Delta V_{BE}}{R_0}$$

$$I_{R1} = \frac{V_{BE1}}{R_1}$$

$$I_{R2} = I_{R1}$$

$$I_2 = I_{R0} + I_{R2}$$

$$I_3 = KI_2 \quad \text{K is the ratio of } I_3 \text{ to } I_2$$

$$V_{REF} = \theta I_3 R_4$$

Substituting, we obtain

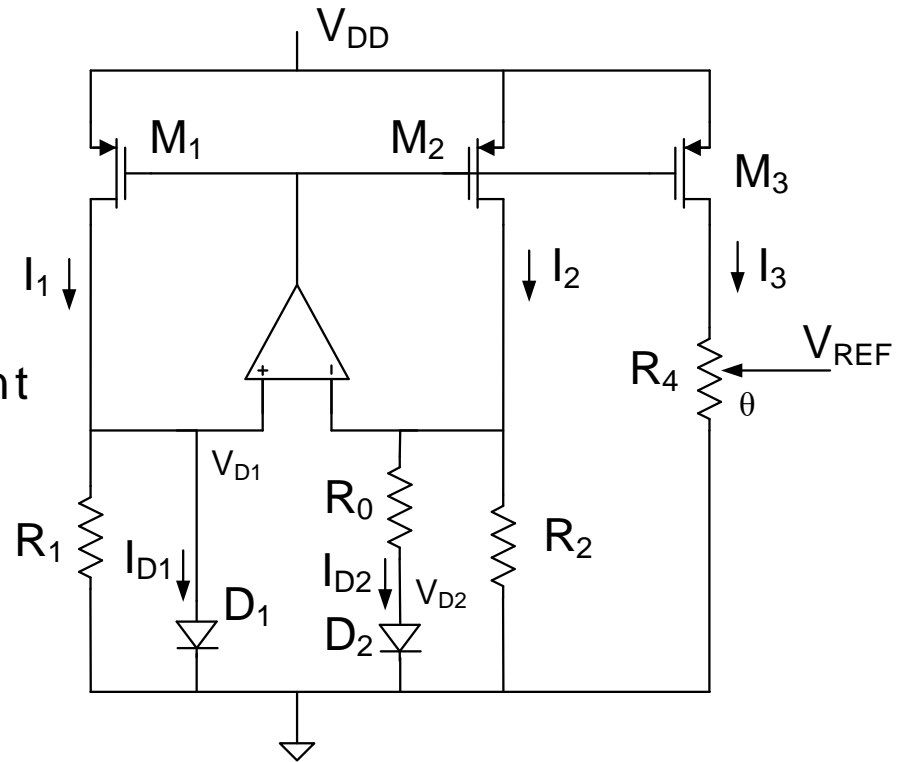
$$V_{REF} = \theta K R_4 \left(\frac{V_{BE}}{R_1} + \frac{\Delta V_{BE}}{R_0} \right)$$



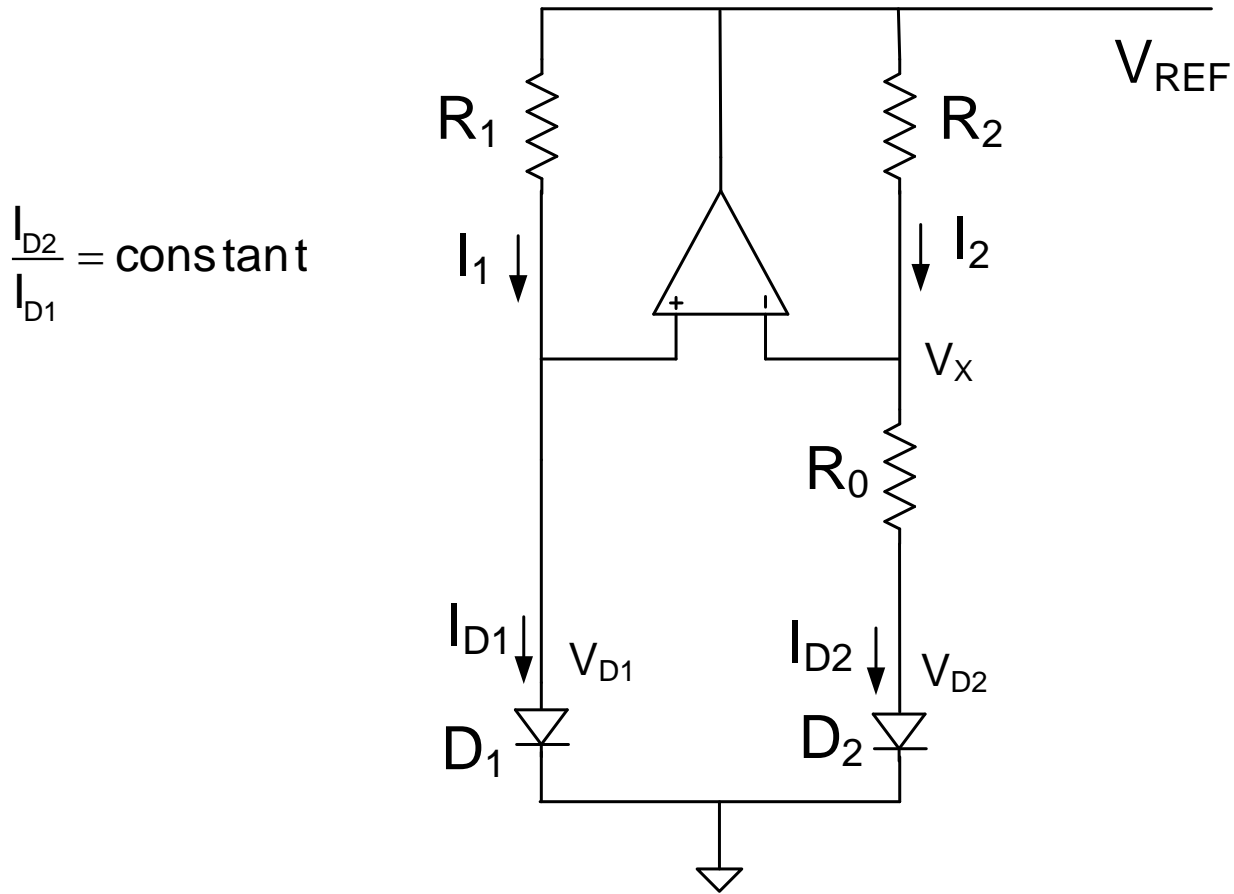
$$V_{REF} = \theta K \frac{R_4}{R_1} \left(V_{BE} + \frac{R_1}{R_0} \Delta V_{BE} \right)$$

$$V_{REF} = a_{11} + b_{11}T + c_{11}T \ln T$$

$$\frac{I_{D2}}{I_{D1}} = \text{constant}$$



Kujik Bandgap Reference



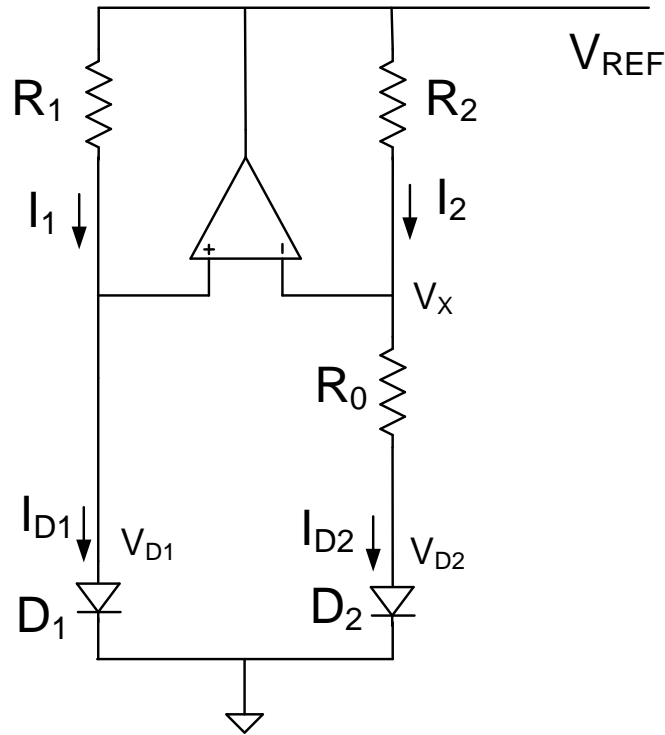
[12] K. Kujik, "A Precision Reference Voltage Source",
IEEE Journal of Solid State Circuits, Vol. 8, pp. 222-226, June
1973.

Kujik Bandgap Reference

$$I_{R0} = \frac{\Delta V_{BE}}{R_0}$$

$$I_2 = I_{R0}$$

$$V_{REF} = I_2 R_2 + V_{BE1}$$



solving, we obtain

$$V_{REF} = \frac{R_2}{R_0} \Delta V_{BE} + V_{BE1}$$

$$V_{REF} = a_{22} + b_{22} T + c_{22} T \ln T$$



<p>Brokaw</p>	<p>Banba</p>
<p>Mietus</p>	<p>Modified Banba</p>
<p>Modified Mietus</p>	<p>Modified Banba</p>

<p>Kuijk</p>	<p>Amema</p>
<p>Modified Kuijk</p>	<p>Zhu</p>

Almost all of the published bandgap references have an output of the form:

$$V_{\text{REF}} = a + bT + cT \ln T$$

	a	b	c
<u>Brokow</u>	$a_1 = V_{G0}$	$b_1 = \frac{k}{q} \left[\frac{R_1}{R_2} \left(1 + \frac{R_2 \alpha_1}{R_1 \alpha_2} \right) \ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left(\frac{k R_2 \alpha_1}{q R_1 \alpha_2} \frac{\ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{J_{SX} R_2} \right) \right]$	$c_1 = \frac{k}{q} (1-m)$
<u>Banba</u>	$a_2 = \left[\frac{R_4 \theta K_3}{R_1} \right] V_{G0}$	$b_2 = \left[\frac{k \theta K_3}{q} \right] \left[\frac{R_4}{R_0} \ln \left(\frac{A_{D2}}{A_{D1}} \right) + \frac{R_4}{R_1} \ln \left(\frac{k}{q} \frac{\ln \left(\frac{A_{D2}}{A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX1}} \right) \right]$	$c_2 = \left[\frac{R_4 \theta K_3}{R_1} \right] \frac{k}{q} (1-m)$
<u>Mieteus</u>	$a_3 = K_5 V_{G0}$	$b_3 = \frac{k}{q} \left[K_3 \frac{R_4}{R_0} \ln \left(K_1 \frac{A_{D2}}{A_{D1}} \right) + K_5 \left[\ln \frac{k}{q} + \frac{\ln \left(K_1 \frac{A_{D2}}{A_{D1}} \right)}{J_{SX} A_{D2}} \right] \right]$	$c_3 = \frac{k}{q} K_5 (1-m)$
<u>Kuijk</u>	$a_4 = V_{G0}$	$b_4 = \frac{k}{q} \left[\frac{R_2}{R_0} \ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left(\frac{R_2}{R_1} \frac{k}{q} \frac{\ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX}} \right) \right]$	$c_4 = \frac{k}{q} (1-m)$
Modified Kuijk	$a_5 = V_{G0}$	$b_5 = \frac{k}{q} \left[\frac{R_2}{R_0} \ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left(\frac{R_2}{R_1} \frac{k}{q} \frac{\ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX}} \right) \right]$	$c_5 = \frac{k}{q} (1-m)$
Modified Kuijk	$a_6 = K V_{G0}$	$b_6 = \frac{k}{q} K \left[\frac{R_2}{R_0} \ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left(\frac{R_2}{R_1} \frac{k}{q} \frac{\ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX}} \right) \right]$	$c_6 = \frac{k}{q} K (1-m)$
<u>Doyle</u>	$a_6 = V_{G0}$	$b_6 = \frac{k}{q} \left[\frac{K_1}{R_1} \frac{R_2}{R_0} \ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \frac{R_2 + R_3}{R_1 + R_2 + R_3} \ln \left(\frac{K_1 k}{R_1 q} \ln \left(\frac{R_2 A_{D2}}{R_1 A_{D1}} \right) \right) - \ln(J_{SX} A_{D2}) \right]$	$c_6 = \frac{k}{q} \left(\frac{R_2 + R_3}{R_1 + R_2 + R_3} - m \right)$

$$V_{REF} = a + bT + cT \ln T$$

- Start-up Circuits Required on all Bandgap References discussed here
- Bandgap circuits widely used to build voltage references for over 4 decades
- Basic bandgap circuits still used today
- Trimming often required to set inflection point at desired temperature
- Offset voltage of Op Amp and TCR of resistors degrade performance
- Experimental performance often a factor of 2 to 10 worse than that predicted here but still quite good
- Ongoing research activities focusing on improving performance of bandgap references



Stay Safe and Stay Healthy !

End of Lecture 39